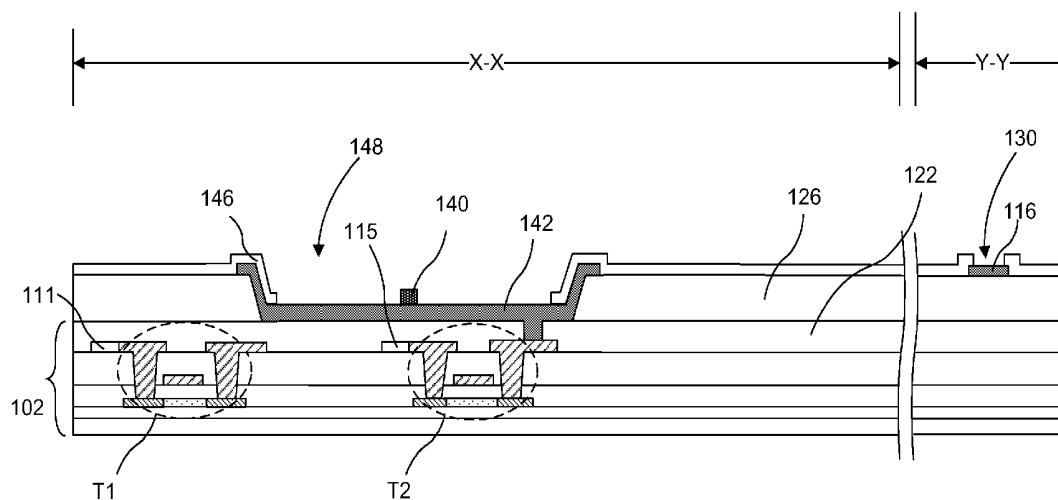


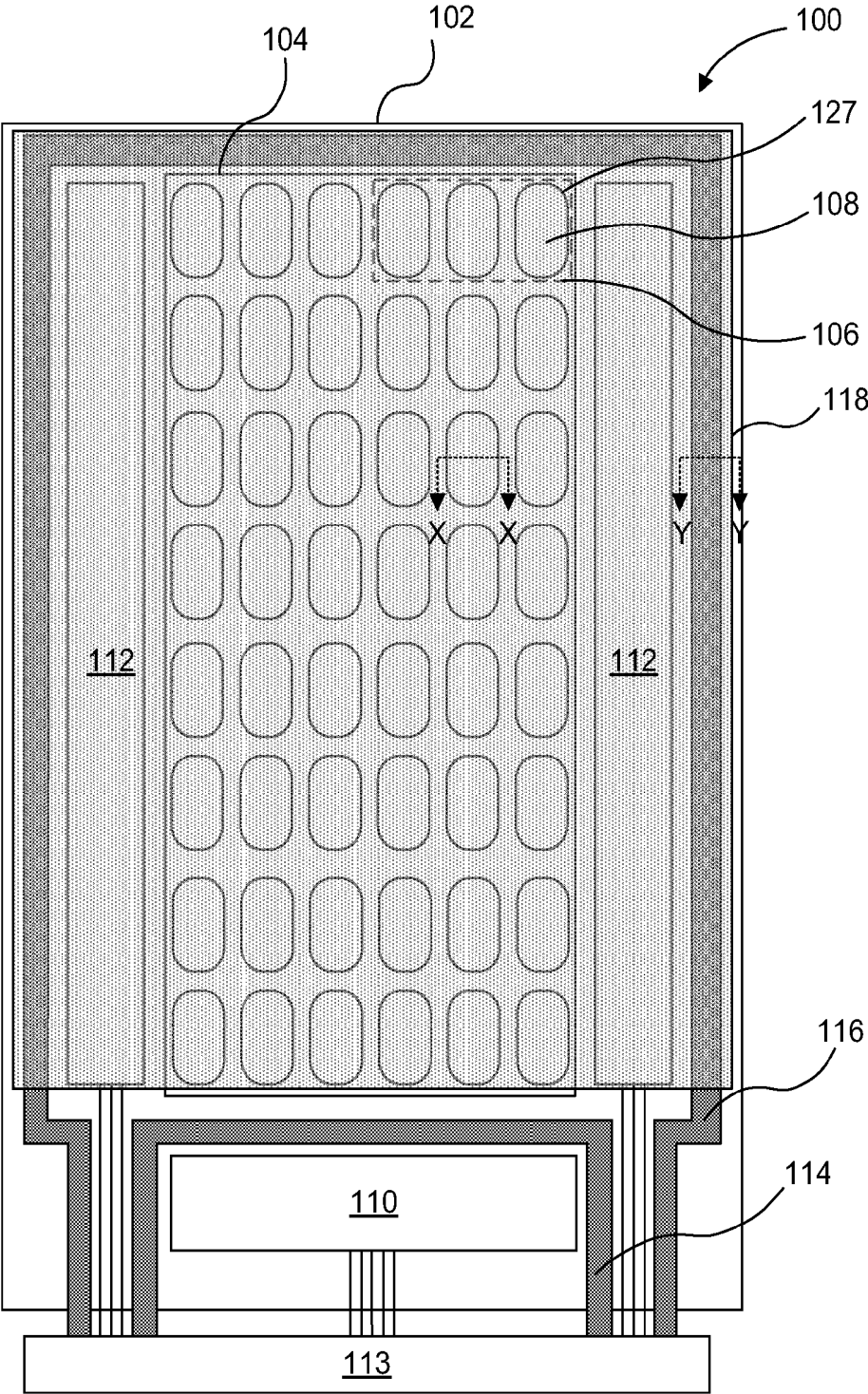


US 20140159067A1

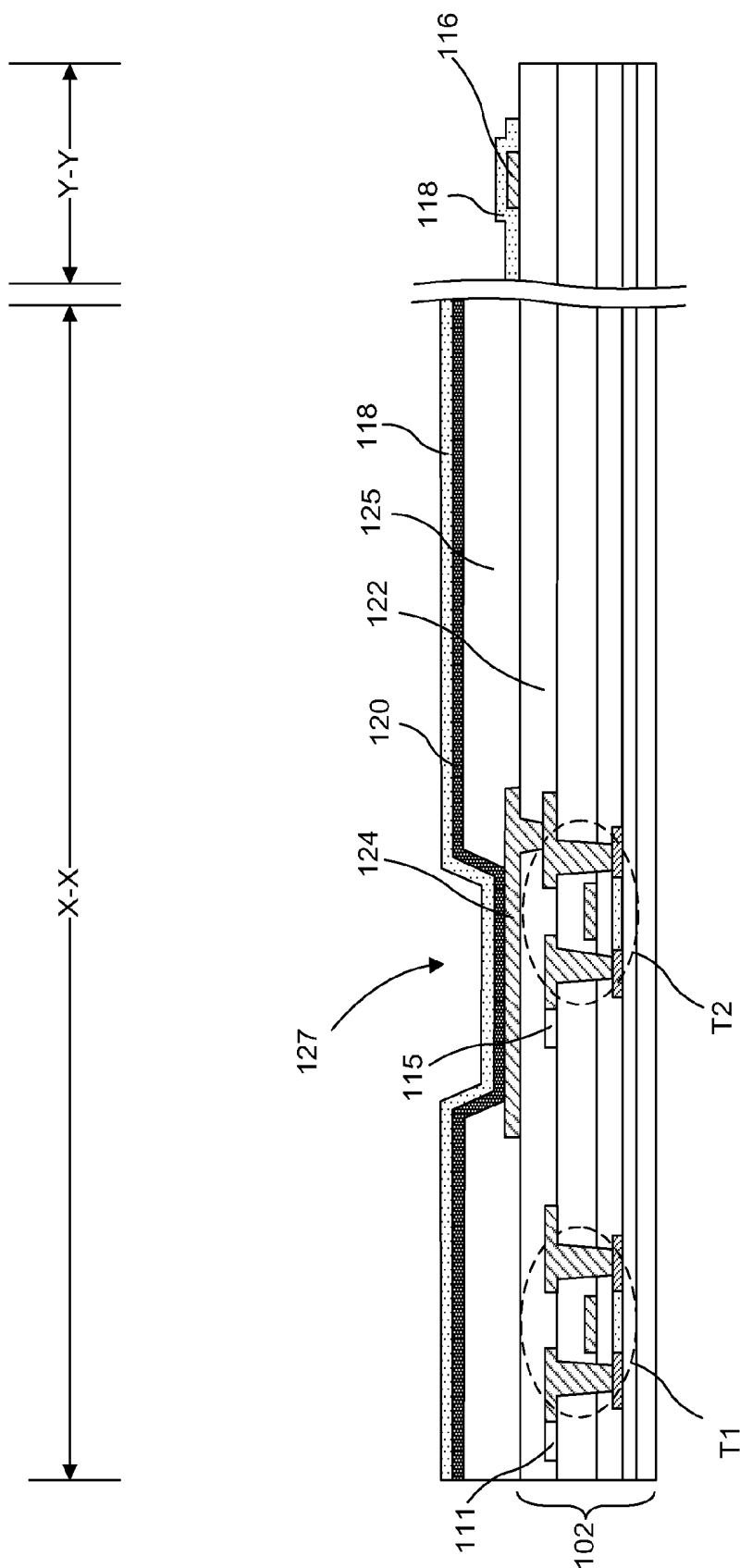
(19) **United States**(12) **Patent Application Publication**  
**Sakariya et al.**(10) **Pub. No.: US 2014/0159067 A1**(43) **Pub. Date: Jun. 12, 2014**(54) **ACTIVE MATRIX EMISSIVE MICRO LED  
DISPLAY****Publication Classification**(71) Applicant: **LUXVUE TECHNOLOGY  
CORPORATION**, Santa Clara, CA  
(US)(51) **Int. Cl.**  
**H01L 27/12** (2006.01)(72) Inventors: **Kapil V. Sakariya**, Sunnyvale, CA (US);  
**Andreas Bibl**, Los Altos, CA (US);  
**Hsin-Hua Hu**, Los Altos, CA (US)(52) **U.S. Cl.**  
CPC ..... **H01L 27/1244** (2013.01); **H01L 27/1292**  
(2013.01)USPC ..... **257/88**; 438/28(73) Assignee: **LUXVUE TECHNOLOGY  
CORPORATION**, Santa Clara, CA  
(US)(57) **ABSTRACT**(21) Appl. No.: **13/842,721**(22) Filed: **Mar. 15, 2013****Related U.S. Application Data**(63) Continuation-in-part of application No. 13/710,443,  
filed on Dec. 10, 2012.

A display panel and a method of forming a display panel are described. The display panel may include a thin film transistor substrate including a pixel area and a non-pixel area. The pixel area includes an array of bank openings and an array of bottom electrodes within the array of bank openings. An array of micro LED devices are bonded to the corresponding array of bottom electrodes within the array of bank openings. An array of top electrode layers are formed electrically connecting the array of micro LED devices to a ground line in the non-pixel area.

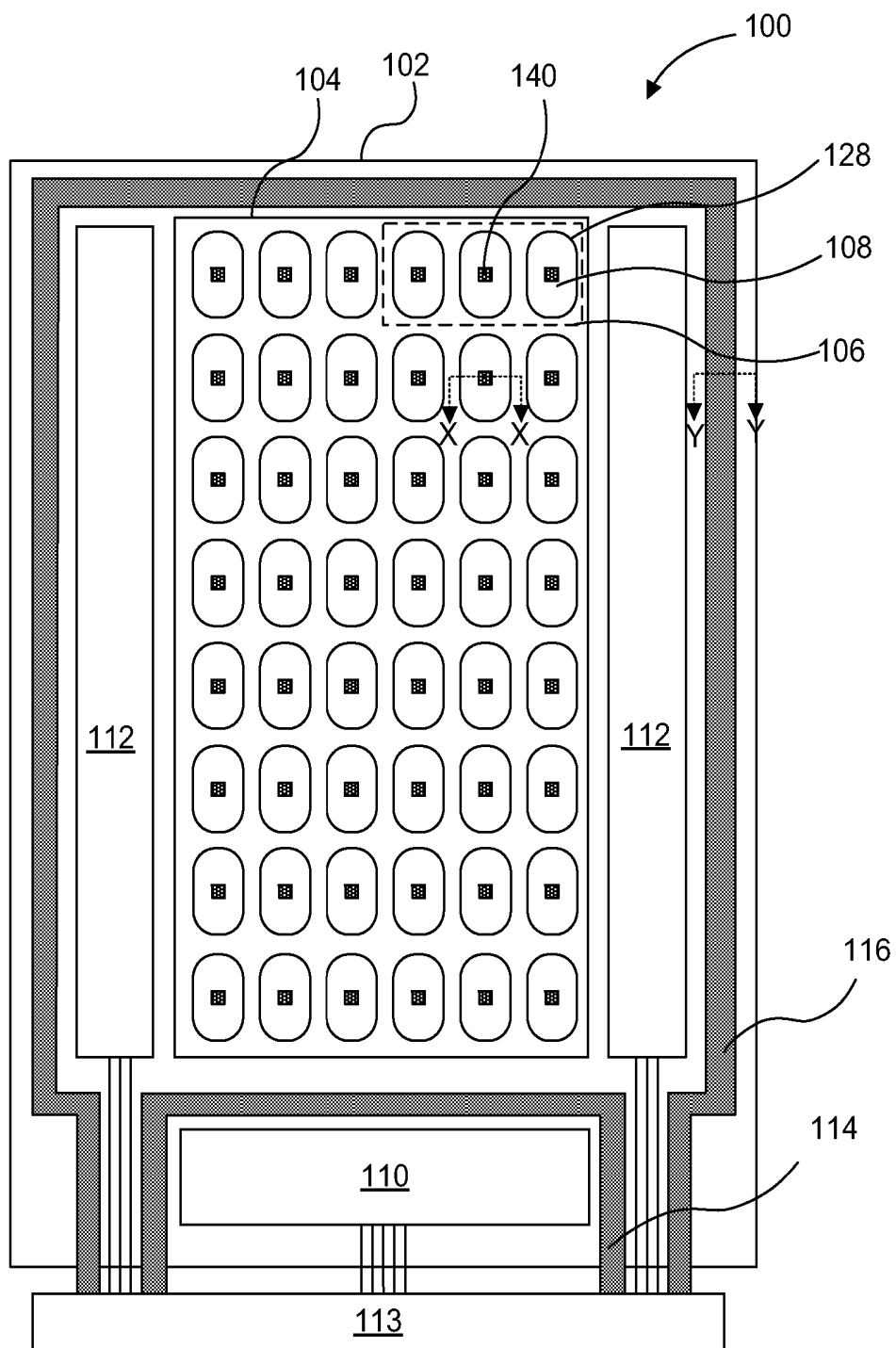




**FIG. 1**  
**PRIOR ART**



**FIG. 2**  
**PRIOR ART**



**FIG. 3A**

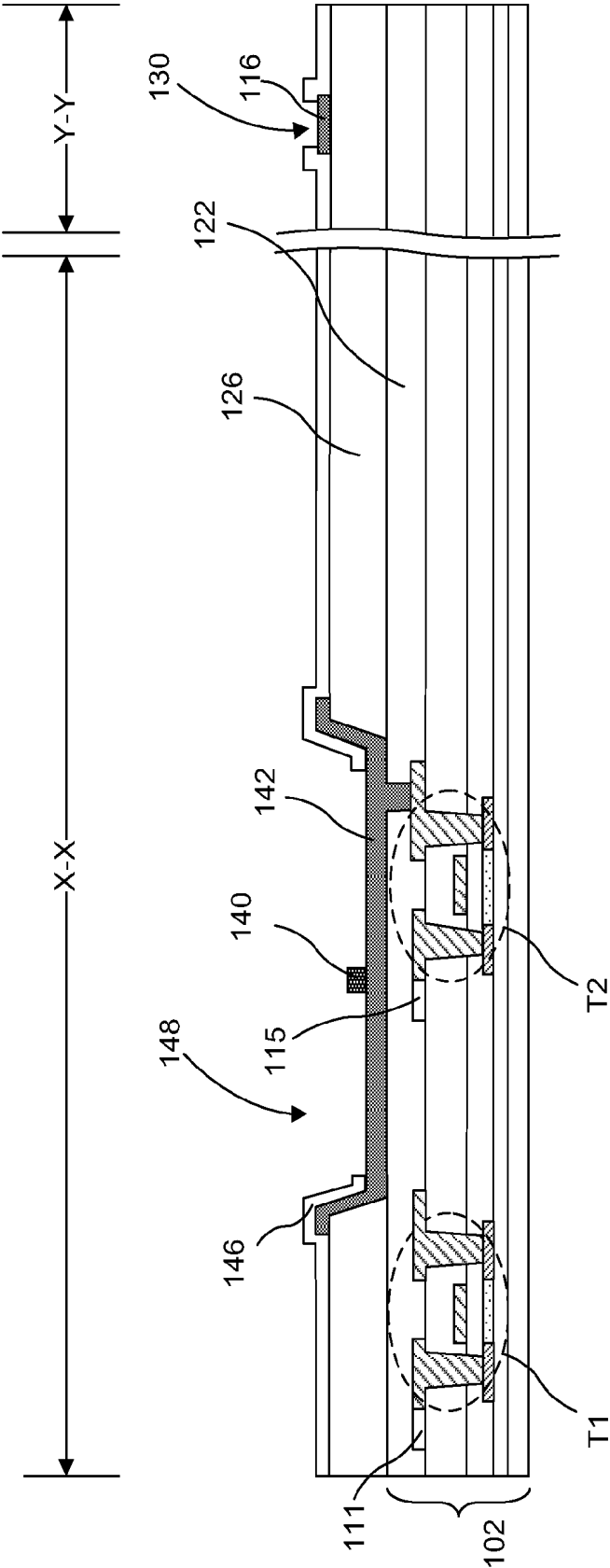


FIG. 3B

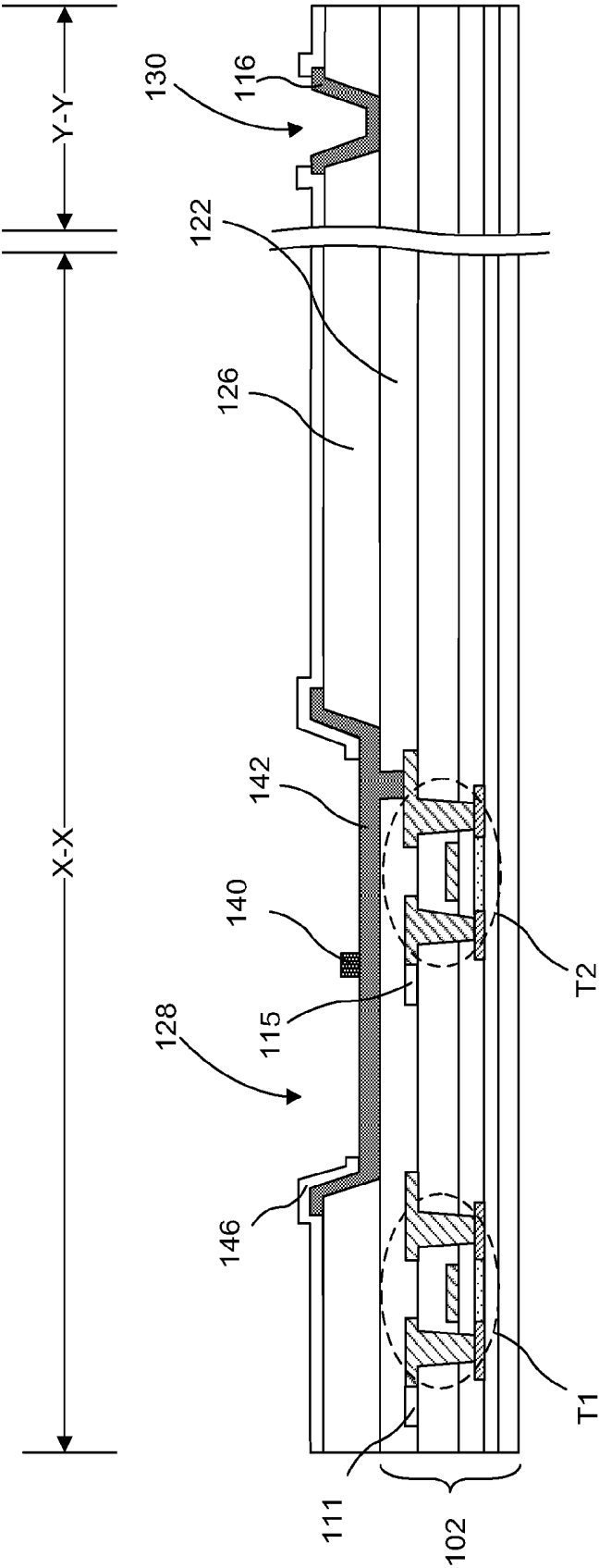


FIG. 3C

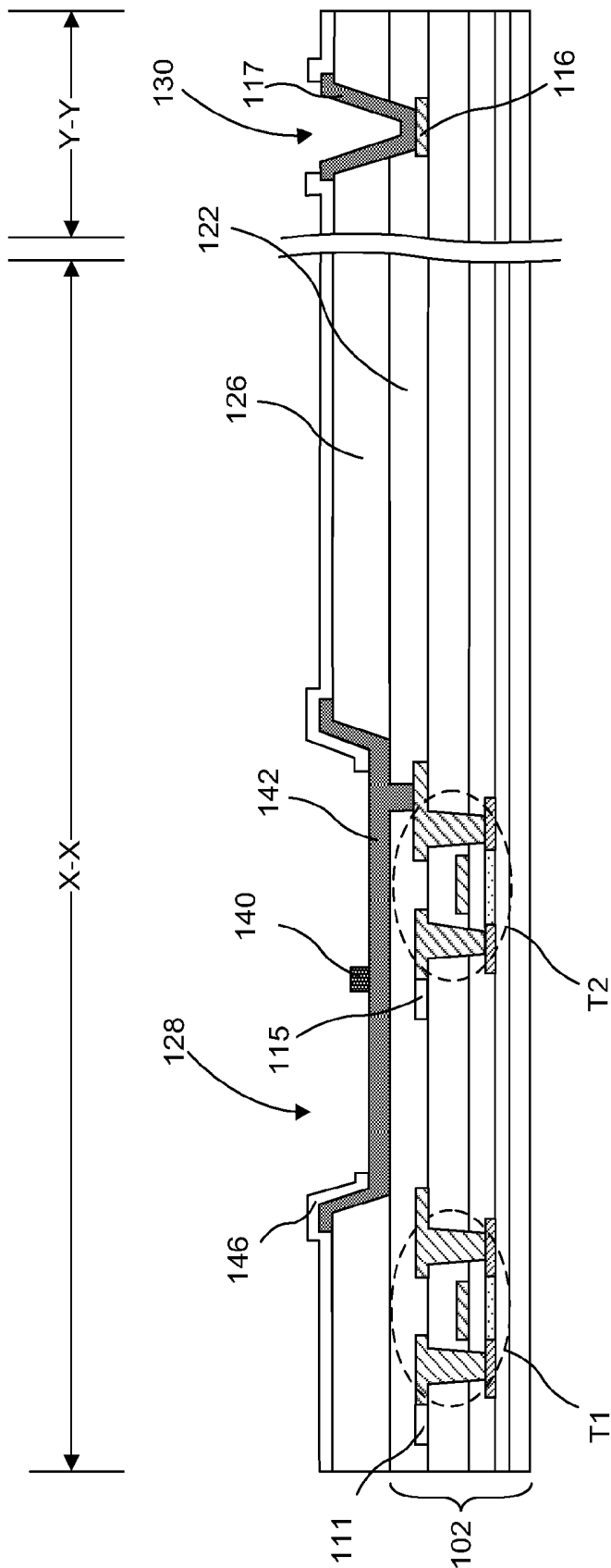


FIG. 3D

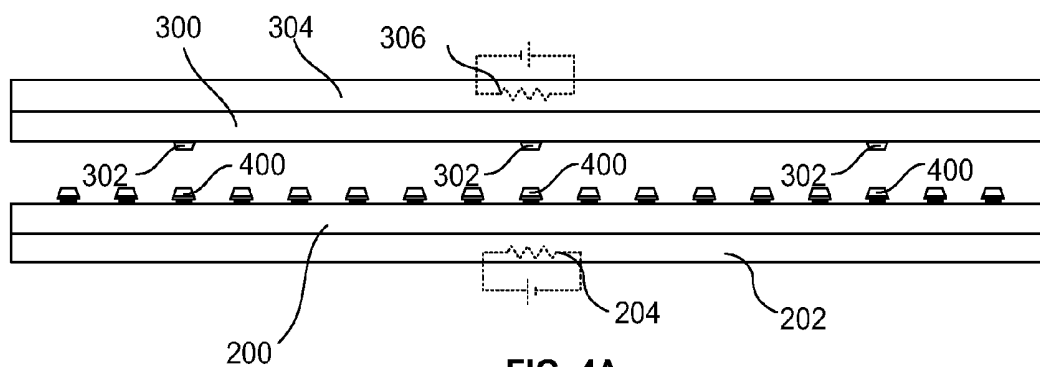


FIG. 4A

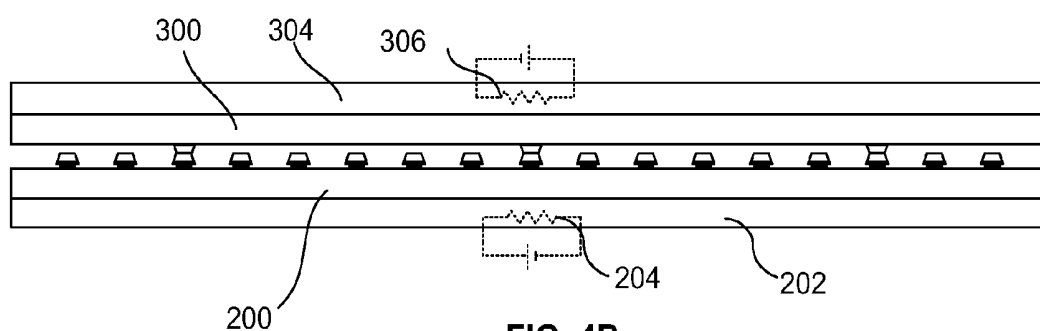


FIG. 4B

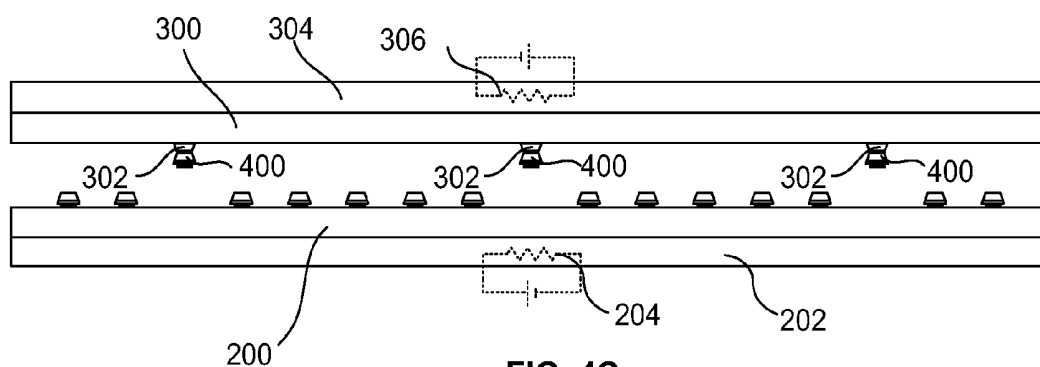
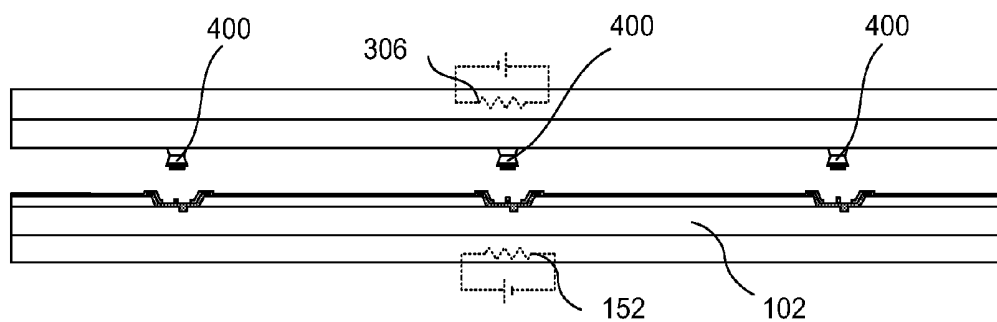
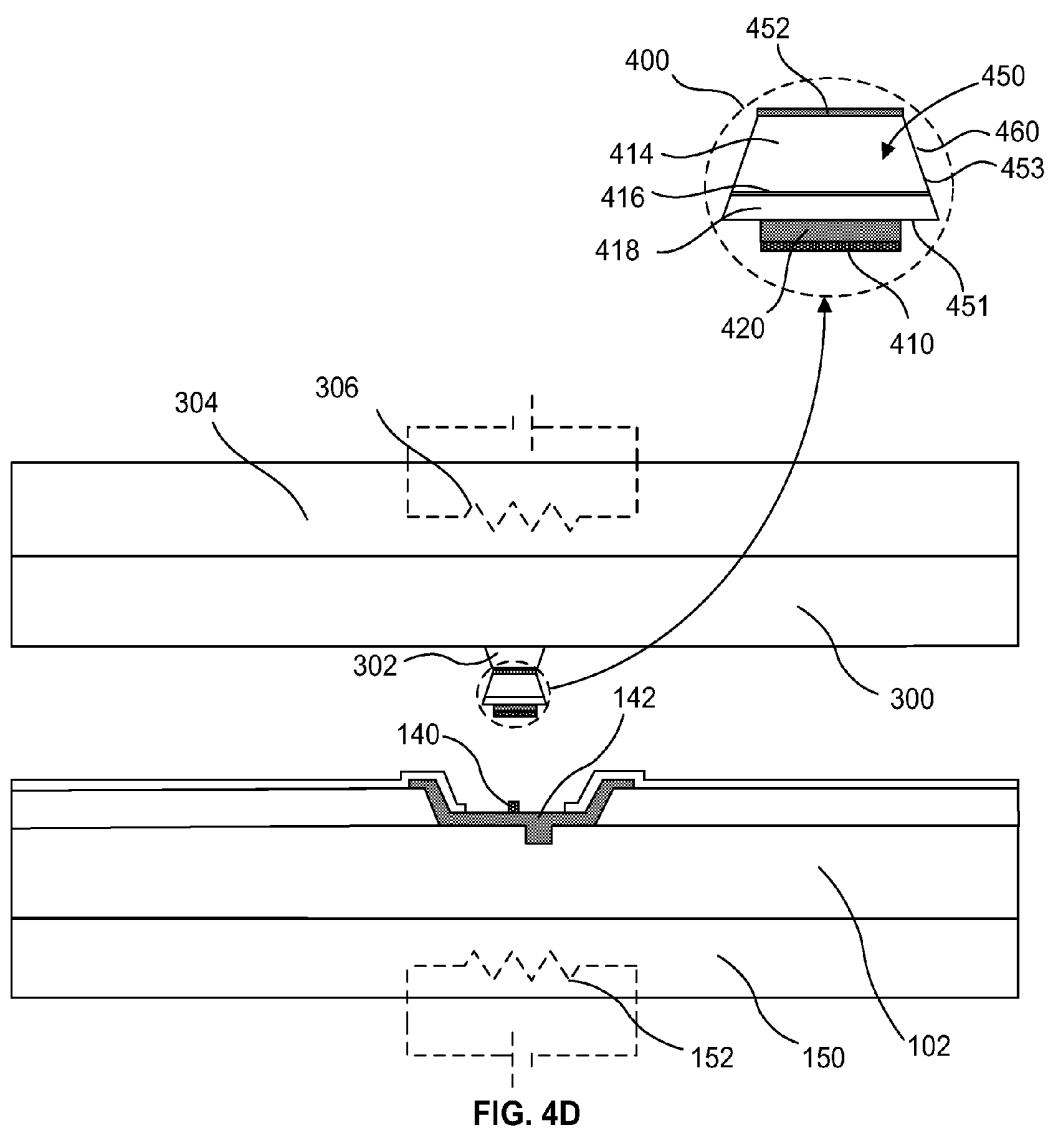


FIG. 4C





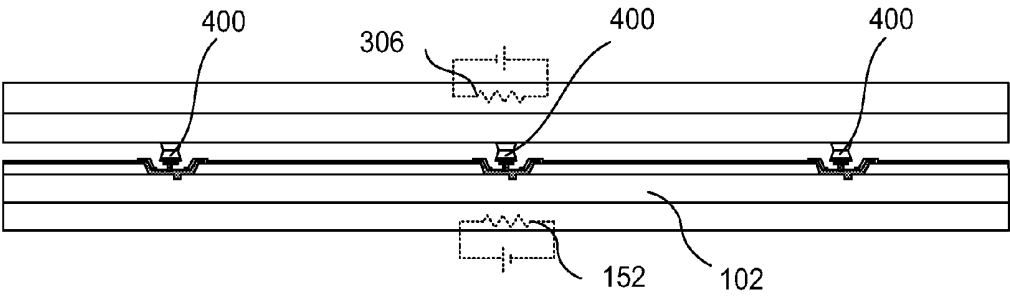


FIG. 4F

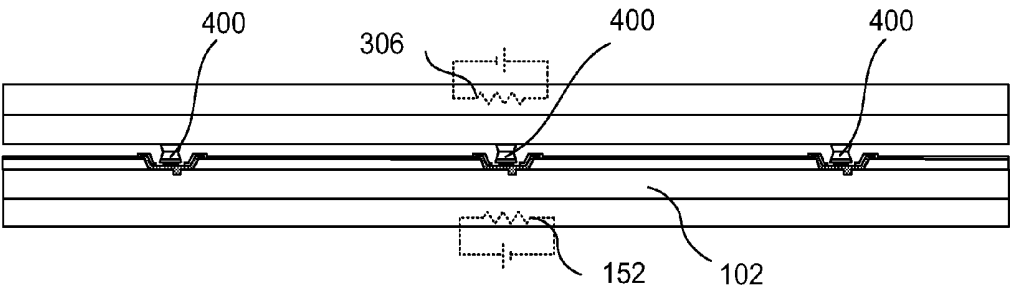


FIG. 4G

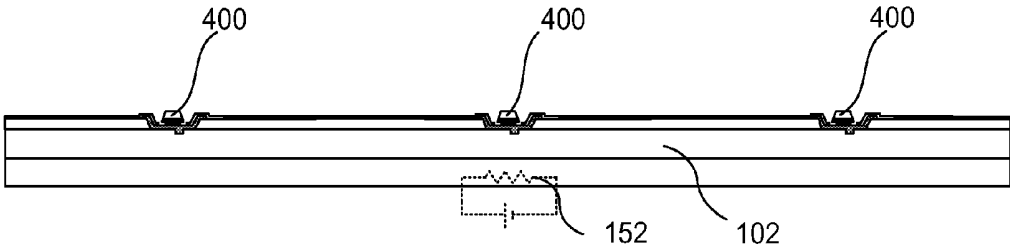


FIG. 4H

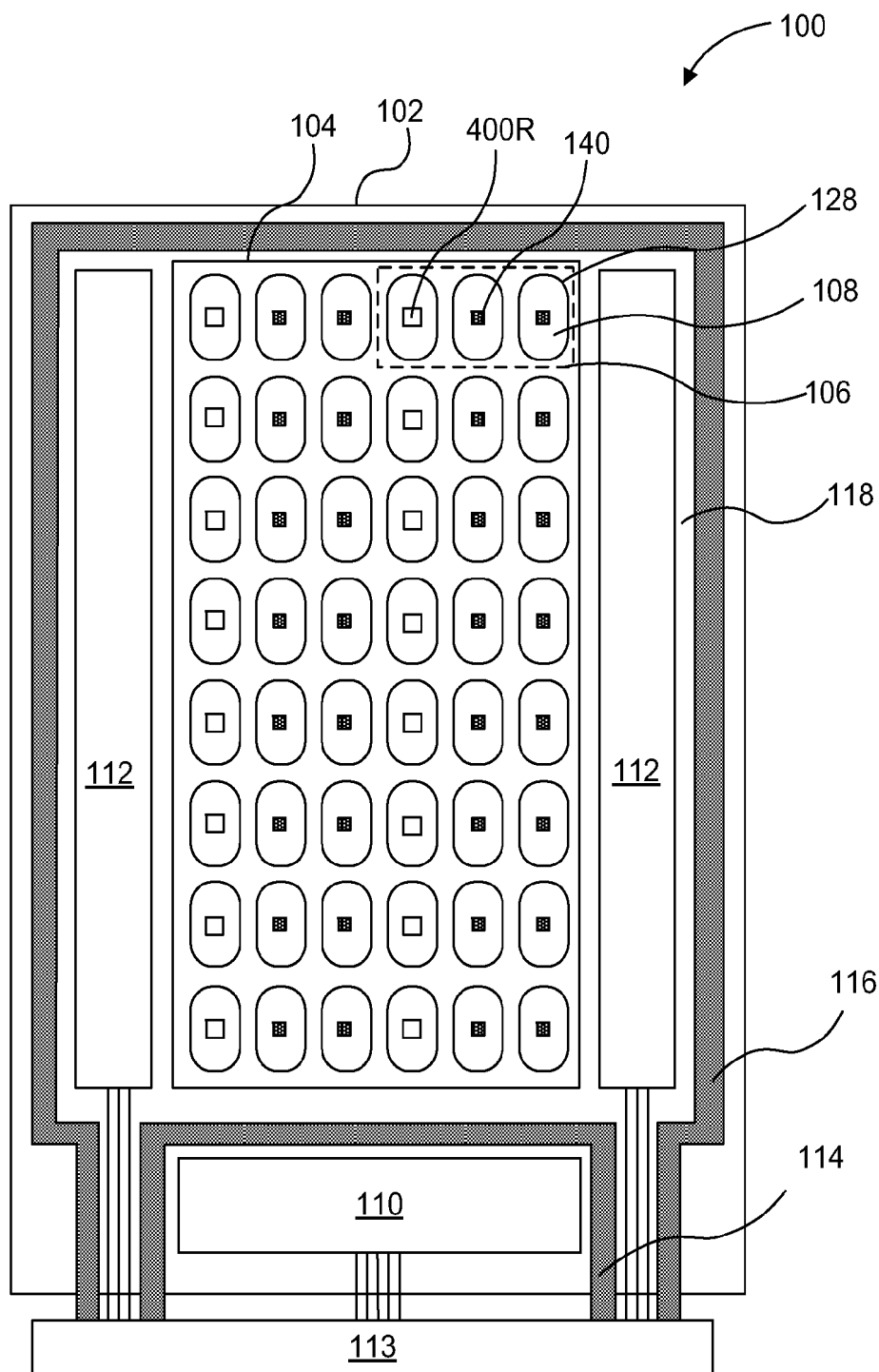


FIG. 5A

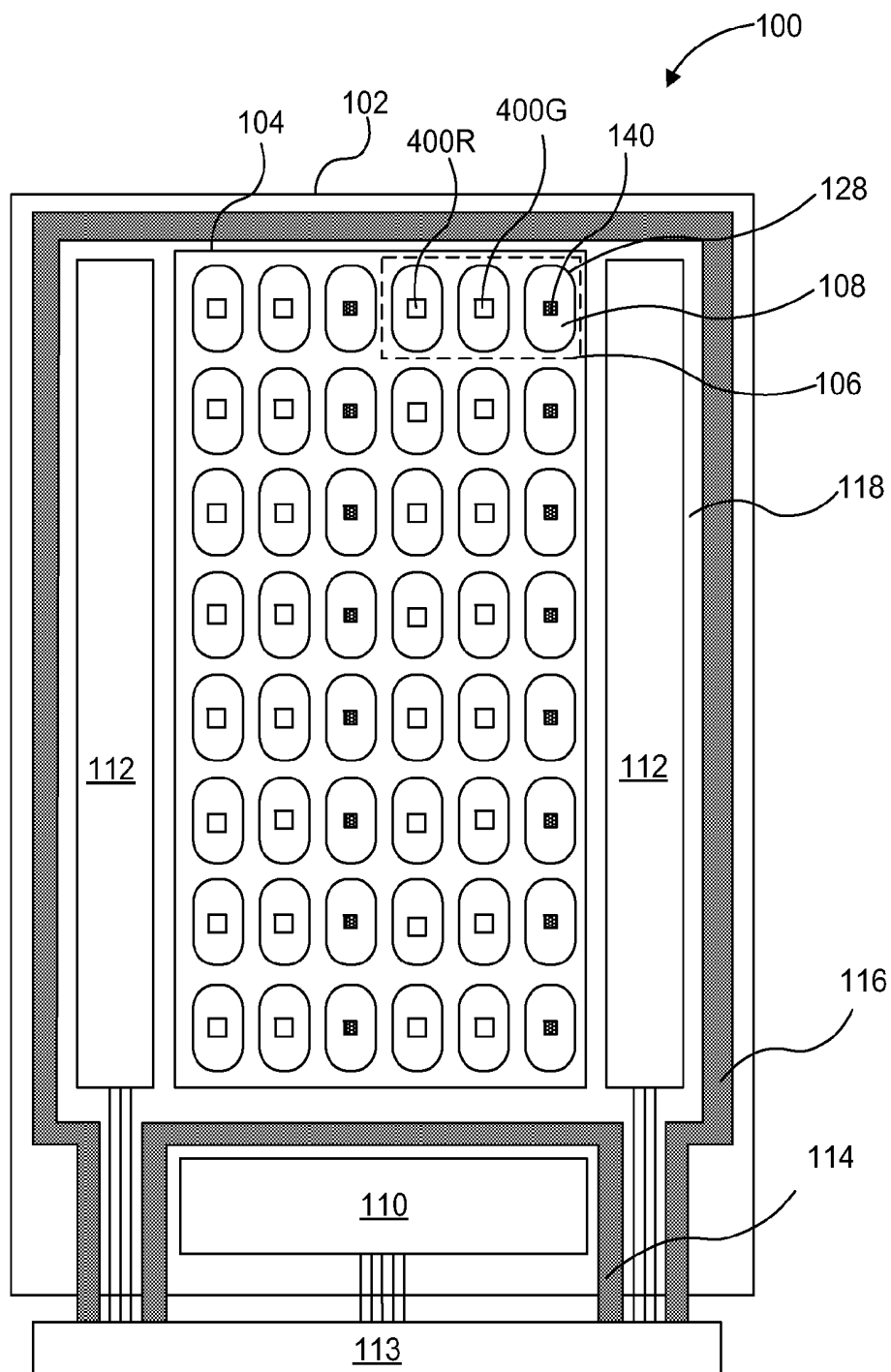


FIG. 5B

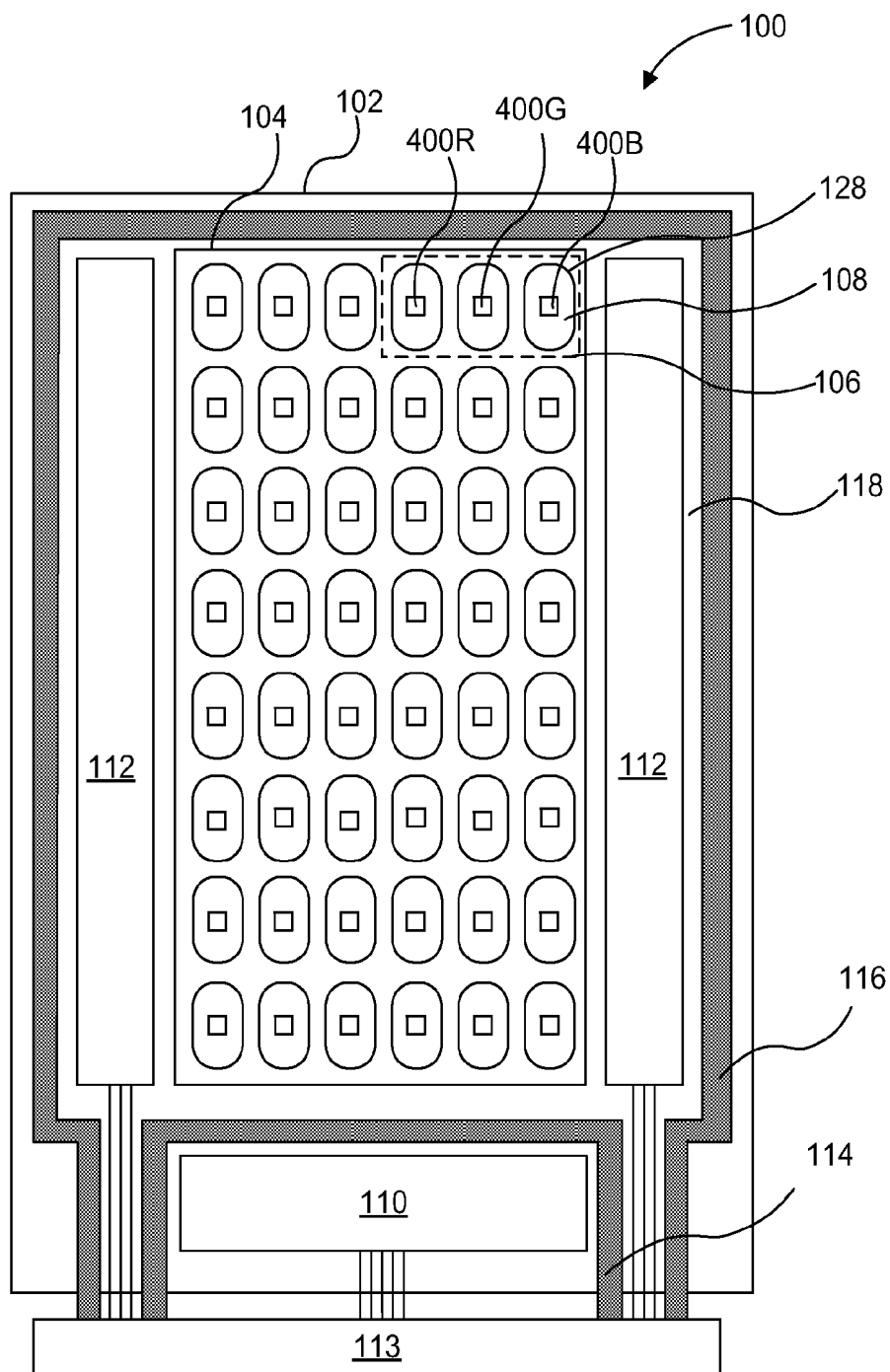


FIG. 5C

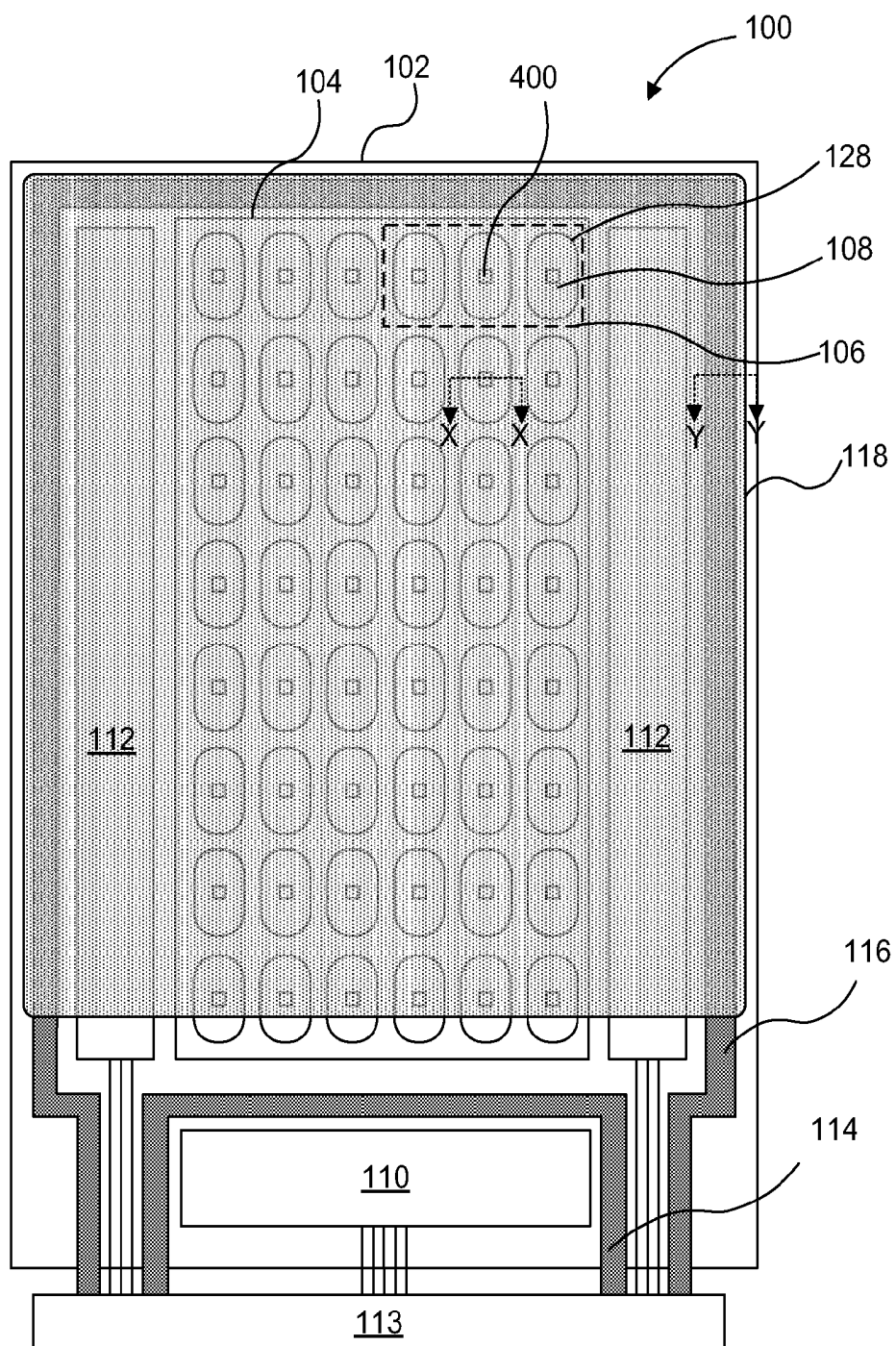


FIG. 6A

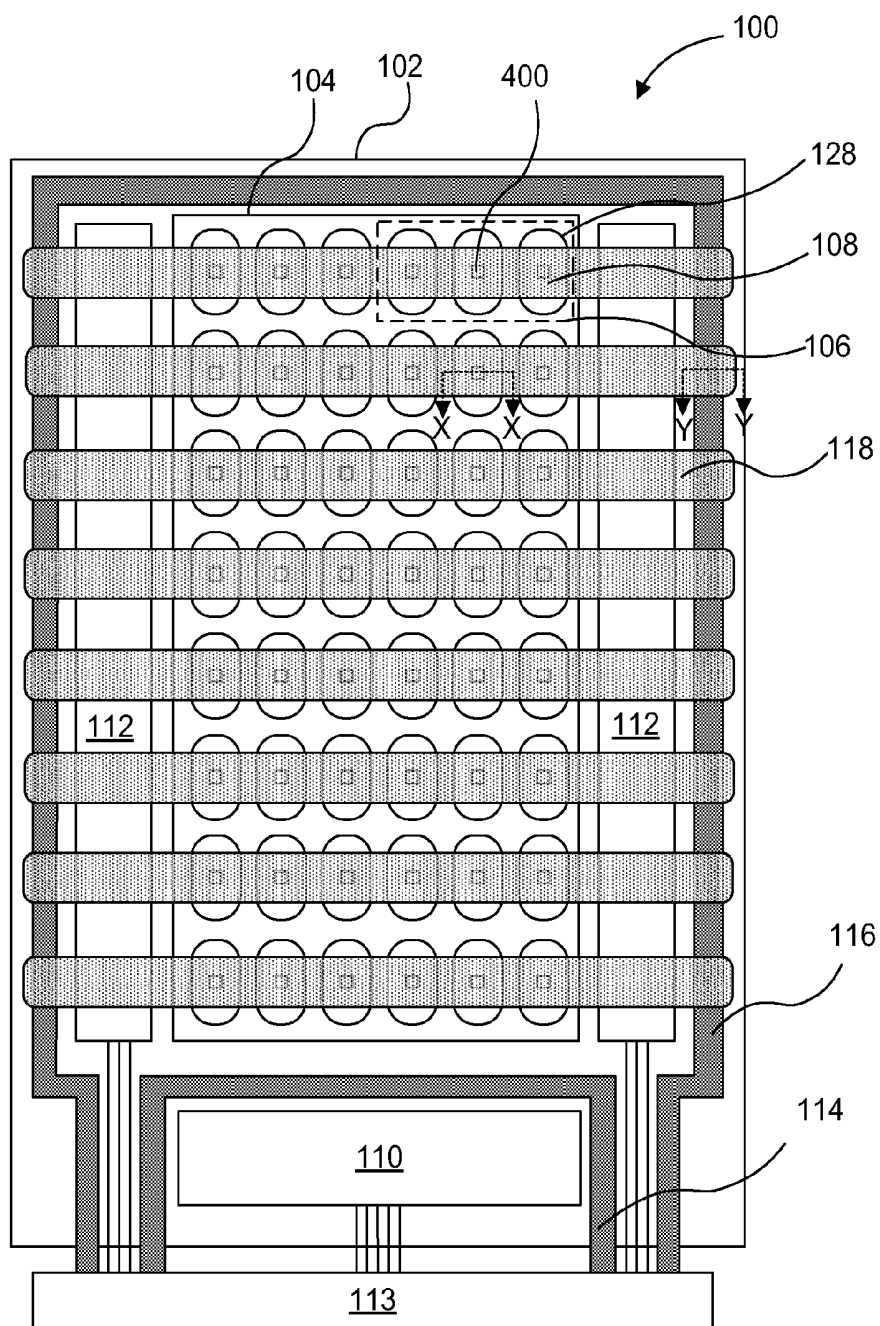


FIG. 6B

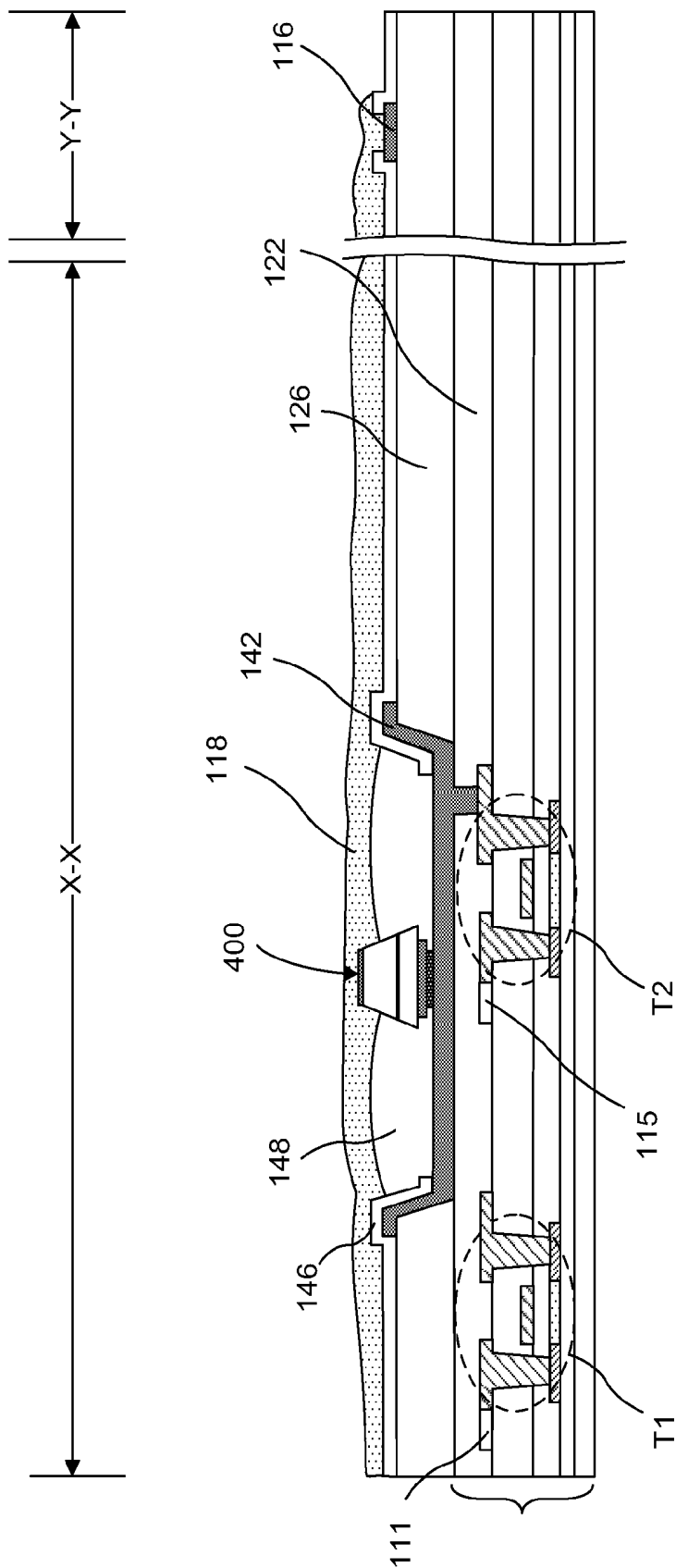
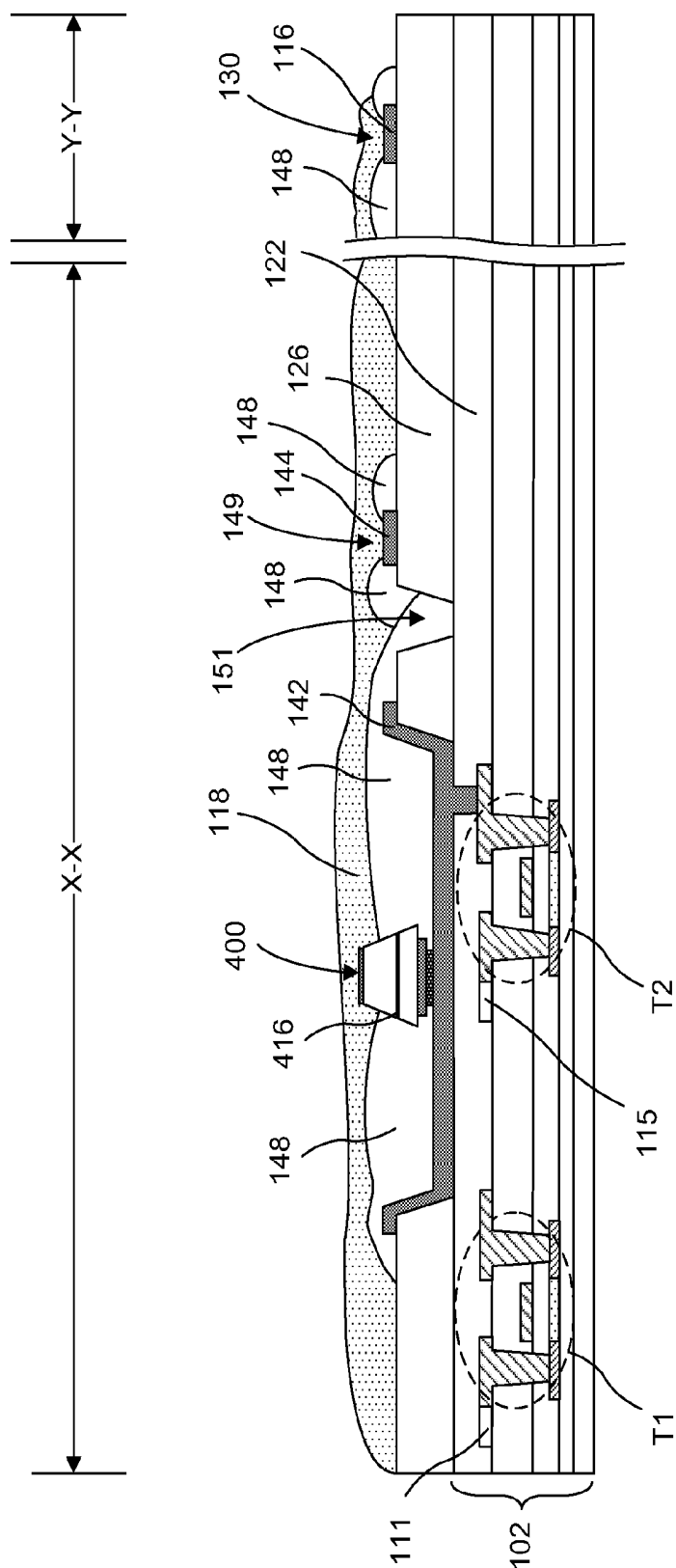
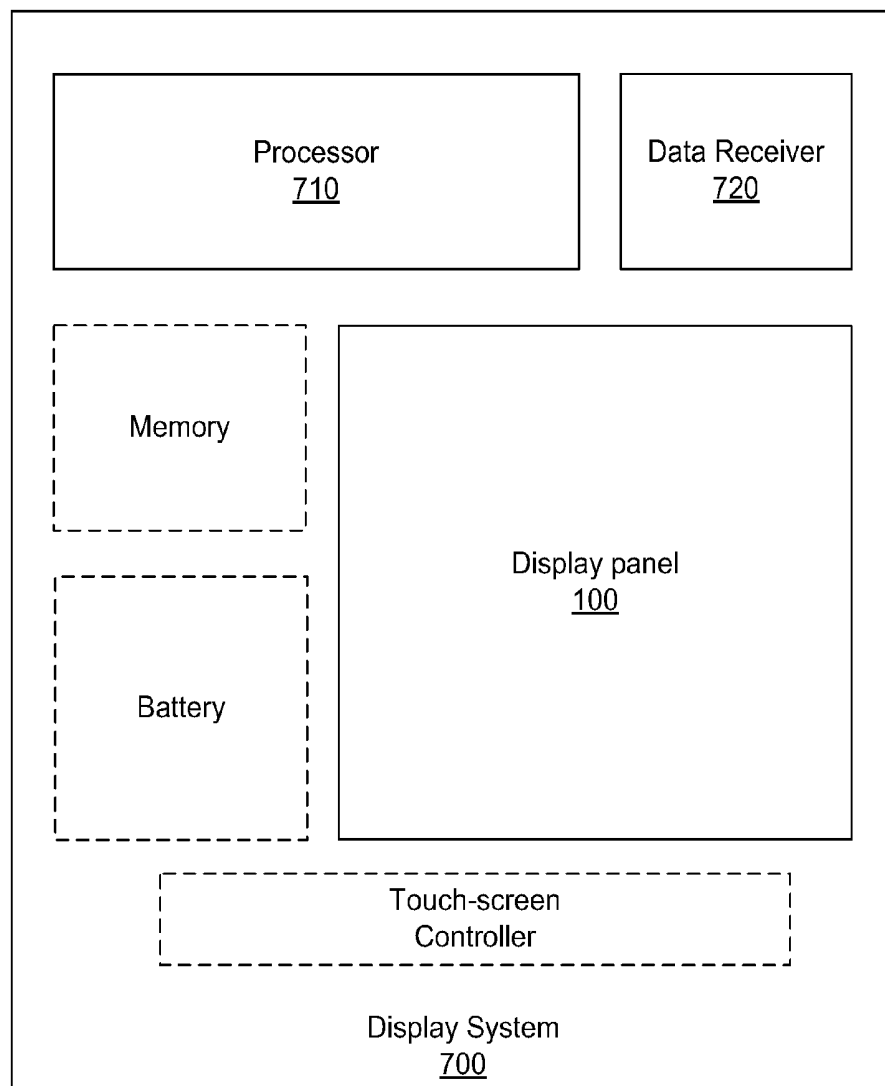


FIG. 6C





**FIG. 6D**

**FIG. 7**

## ACTIVE MATRIX EMISSIVE MICRO LED DISPLAY

### RELATED APPLICATIONS

**[0001]** This application is a continuation-in-part of U.S. patent application Ser. No. 13/710,443 filed on Dec. 10, 2012, which is incorporated herein by reference.

### BACKGROUND

**[0002]** 1. Field

**[0003]** Embodiments of the present invention relate to display systems. More particularly embodiments of the present invention relate to a grounding structure for an active matrix display panel.

**[0004]** 2. Background Information

**[0005]** Flat panel displays are gaining popularity in a wide range of electronic devices. Common types of flat panel displays include active matrix displays and passive matrix displays. Each pixel in an active matrix display panel is driven by active driving circuitry, while each pixel in a passive matrix display panel does not use such driving circuitry. High-resolution color display panels, such as modern computer displays, smart phones and televisions typically use an active matrix display panel structure for better image quality.

**[0006]** One kind of display panel that is finding commercial application is an active matrix organic light emitting diode (AMOLED) display panel. FIG. 1 is a top view illustration of a top emission AMOLED display panel. FIG. 2 is a cross-sectional side view illustration of FIG. 1 taken along line X-X in the pixel area **104** and line Y-Y crossing the ground ring **116** in the non-pixel area. The AMOLED display panel **100** illustrated in FIGS. 1-2 generally includes a thin film transistor (TFT) substrate **102** supporting a pixel area **104** and non-pixel area outside of the pixel area **102**. A TFT substrate **102** is also referred to as a backplane. A TFT substrate which has been further processed to additionally include the pixel area and non-pixel area is also often referred to as a backplane. Two primary TFT substrate technologies used in AMOLEDs include polycrystalline silicon (poly-Si) and amorphous silicon (a-Si). These technologies offer the potential for fabricating the active matrix backplanes at low temperatures (below 200° C.) directly onto flexible plastic substrates for producing flexible AMOLED displays. The pixel area **104** generally includes pixels **106** and subpixels **108** arranged in a matrix, and a set of TFTs and capacitors connected to each subpixel for driving and switching the subpixels. The non-pixel area generally includes a data driver circuit **110** connected to a data line of each subpixel to enable data signals (Vdata) to be transmitted to the subpixels, a scan driver circuit **112** connected to scan lines of the subpixels to enable scan signals (Vscan) to be transmitted to the subpixels, a power supply line **114** to transmit a power signal (Vdd) to the TFTs, and a ground ring **116** to transmit a ground signal (Vss) to the array of subpixels. As shown, the data driver circuit, scan driver circuit, power supply line, and ground ring are all connected to a flexible circuit board (FCB) **113** which includes a power source for supplying power to the power supply line **114** and a power source ground line electrically connected to the ground ring **116**.

**[0007]** In the exemplary AMOLED backplane configuration an organic thin film **120** and top electrode **118** are deposited over every subpixel **108** in the pixel area **104**. The organic thin film **120** may include multiple layers such as a hole

injection layer, hole transport layer, light emitting layer, electron transport layer, and electron injection layer. The multiple layers of the organic thin film **120** are typically formed over the entire pixel area **104**, however, the light emitting layer is often deposited with aid of a shadow mask only within the subpixel openings **127** and on the bottom electrode layer **124** corresponding to the emission area for the array of subpixels **108**. A top electrode layer **118** is then deposited over the organic thin film within both the pixel area **104** and also within the non-pixel area so that the top electrode **118** layer overlaps the ground ring **116** in the in order to transfer the ground signal to the array of subpixels. In this manner, each of the subpixels **108** can be individually addressed with the corresponding underlying TFT circuitry while a uniform ground signal is supplied to the top of the pixel area **104**.

**[0008]** In the particular implementation illustrated, the TFT substrate **102** includes a switching transistor T1 connected to a data line **111** from the data driver circuit **110** and a driving transistor T2 connected to a power line **115** connected to the power supply line **114**. The gate of the switching transistor T1 may also be connected to a scan line (not illustrated) from the scan driver circuit **112**. A planarization layer **122** is formed over the TFT substrate, and openings are formed to expose the TFT working circuitry. As illustrated, a bottom electrode layer **124** is formed on the planarization layer in electrical connection with the TFT circuitry. Following the formation of the electrode layer a pixel defining layer **125** is formed including an array of subpixel openings **127** corresponding to the emission area for the array of subpixels **108**, followed by deposition of the organic layer **120** and top electrode layer **118** over the patterned pixel defining layer, and within subpixel openings **127** of the patterned pixel defining layer **125**. The top electrode layer **118** additionally is formed in the non-pixel area and in electrical connection with the ground ring **116**.

**[0009]** The planarization layer **122** may function to prevent (or protect) the organic layer **120** and the bottom electrode layer **124** from shorting due to a step difference. Exemplary planarization layer **122** materials include benzocyclobutene (BCB) and acrylic. The pixel defining layer **125** can be formed of a material such as polyimide. The bottom electrode **124** is commonly formed on indium tin oxide (ITO), ITO/Ag, ITO/Ag/ITO, ITO/Ag/indium zinc oxide (IZO), or ITO/Ag alloy/ITO. The top electrode layer **118** is formed of a transparent material such as ITO for top emission.

**[0010]** While AMOLED display panels generally consume less power than liquid crystal display (LCD) panels, an AMOLED display panel can still be the dominant power consumer in battery-operated devices. To extend battery life, it is necessary to reduce the power consumption of the display panel.

### SUMMARY OF THE INVENTION

**[0011]** A display panel and a method of forming a display panel are described. In an embodiment a display panel includes a TFT substrate including a pixel area and a non-pixel area. For example, the non-pixel area may surround the pixel area. The pixel area includes an array of bank openings and an array of bottom electrodes within the array of bank openings. The array of bottom electrodes may be formed on sidewalls of the corresponding array of bank openings, and may be reflective to the visible wavelength. In an embodiment a post of solder material is formed on the bottom electrode within each bank opening in order to aid the bonding of a

micro LED device to the bottom electrode. A ground line is formed in the non-pixel area. In an embodiment, the ground line is a ground ring. In an embodiment a patterned insulator layer covers the array of bottom electrodes, and an array of openings is formed in the patterned insulator exposing the array of bottom electrodes. In this manner, the patterned insulator layer may cover the edges of the array of bottom electrodes.

**[0012]** In an embodiment, an array of micro LED devices are on the array of bottom electrodes within the corresponding array of bank openings. For example, the micro LED devices may be vertical micro LED devices, and may have a maximum width of 1  $\mu\text{m}$ -100  $\mu\text{m}$ . A transparent passivation layer can be formed spanning sidewalls of the array of micro LED devices without completely covering a top conductive contact of each micro LED device. In an embodiment, an array of top electrode layers are formed over the array of micro LED devices electrically connecting the array of micro LED devices to the ground line. For example, each top electrode layer may span over a single row of micro LED devices. Each top electrode may span over a plurality of rows of micro LED devices. In an embodiment, the each top electrode layer is electrically connected to the ground ring on opposite sides of the pixel area. The top electrode layers may also be formed of a transparent or semi-transparent material such as PEDOT or ITO.

**[0013]** In an embodiment, a method of forming a display panel includes transferring an array of micro LED devices from a carrier substrate to a backplane that comprises a TFT substrate including a pixel area and a non-pixel area, where the pixel area includes an array of bank openings and an array of bottom electrodes within the array of bank openings. The TFT substrate also includes a ground line in the non-pixel area. In an embodiment, an array of separate top electrode layers are formed over the array micro LED devices electrically connecting the array of micro LED devices to the ground line. In an embodiment, top electrode layers are formed by ink jet printing or screen printing. In an embodiment, the ground line is a ground ring and the array of separate top electrode layers span between opposite sides of the ground ring. In accordance with embodiments of the invention, each top electrode layer may span over one or more rows of micro LED devices. For example, each top electrode layer may span over a single row of micro LED device, or may span over a plurality of rows of micro LED devices. It is not required for the top electrode layers to completely cover the pixel area of the TFT substrate.

**[0014]** In an embodiment, transfer of the array of micro LED device is performed with electrostatic principles using an array of electrostatic transfer heads. Furthermore, bonding of the array of micro LED devices may include the formation of an inter-metallic compound, and may include liquefying an array of bonding layers formed on the array of bottom electrodes. Bonding and liquefying may be accomplished in part by the transfer of thermal energy from the array of electrostatic transfer heads to the array of bonding layers formed on the array of bottom electrodes.

#### BRIEF DESCRIPTION OF THE DRAWINGS

**[0015]** FIG. 1 is a top view illustration of a top emission AMOLED display panel.

**[0016]** FIG. 2 is a side-view illustration of the top emission AMOLED display panel of FIG. 1 taken along lines X-X and Y-Y.

**[0017]** FIG. 3A is a top view illustration of an active matrix display panel in accordance with an embodiment of the invention.

**[0018]** FIG. 3B is a side-view illustration of the active matrix display panel of FIG. 3A taken along lines X-X and Y-Y in accordance with an embodiment of the invention.

**[0019]** FIG. 3C is a side-view illustration of the active matrix display panel of FIG. 3A taken along lines X-X and Y-Y in accordance with an embodiment of the invention in which a ground ring is formed within a patterned bank layer.

**[0020]** FIG. 3D is a side-view illustration of the active matrix display panel of FIG. 3A taken along lines X-X and Y-Y in accordance with an embodiment of the invention in which a ground ring is formed below a patterned bank layer.

**[0021]** FIGS. 4A-4H are cross-sectional side view illustrations for a method of transferring an array of micro LED devices to a TFT substrate in accordance with an embodiment of the invention.

**[0022]** FIGS. 5A-5C are top view illustrations for a sequence of transferring an array of micro LED devices with different color emissions in accordance with an embodiment of the invention.

**[0023]** FIG. 6A is a top view illustration of an active matrix display panel after the formation of a top electrode layer in accordance with an embodiment.

**[0024]** FIG. 6B is a top view illustration of an active matrix display panel after the formation of separate top electrode layers in accordance with an embodiment.

**[0025]** FIG. 6C is a side-view illustration of the active matrix display panel of either FIG. 6A or FIG. 6B taken along lines X-X and Y-Y in accordance with an embodiment of the invention.

**[0026]** FIG. 6D is a side-view illustration of the active matrix display panel of either FIG. 6A or FIG. 6B taken along lines X-X and Y-Y in accordance with an embodiment of the invention.

**[0027]** FIG. 7 is a schematic illustration of a display system in accordance with an embodiment of the invention.

#### DETAILED DESCRIPTION OF THE INVENTION

**[0028]** Embodiments of the present invention relate to display systems. More particularly embodiments of the present invention relate to an active matrix display panel including emissive micro LEDs.

**[0029]** In one aspect, embodiments of the invention describe an active matrix display panel including wafer-based emissive micro LED devices. A micro LED device combines the performance, efficiency, and reliability of wafer-based LED devices with the high yield, low cost, mixed materials of thin film electronics used to form AMOLED backplanes. The terms "micro" device or "micro" LED structure as used herein may refer to the descriptive size of certain devices or structures in accordance with embodiments of the invention. As used herein, the terms "micro" devices or structures are meant to refer to the scale of 1 to 100  $\mu\text{m}$ . However, it is to be appreciated that embodiments of the present invention are not necessarily so limited, and that certain aspects of the embodiments may be applicable to larger, and possibly smaller size scales. In an embodiment, a display panel is similar to a typical OLED display panel, with a micro LED device having replaced the organic layer of the OLED display panel in each subpixel. Exemplary micro LED devices which may be utilized with some embodiments of the invention are described in U.S. patent application Ser. No. 13/372,222, U.S. patent

application Ser. No. 13/436,260, U.S. patent application Ser. No. 13/458,932, U.S. patent application Ser. No. 13/711,554, and U.S. patent application Ser. No. 13/749,647 all of which are incorporated herein by reference. The micro LED devices are highly efficient at light emission and consume very little power (e.g., 250 mW for a 10 inch diagonal display) compared to 5-10 watts for a 10 inch diagonal LCD or OLED display, enabling reduction of power consumption of the display panel.

**[0030]** In various embodiments, description is made with reference to figures. However, certain embodiments may be practiced without one or more of these specific details, or in combination with other known methods and configurations. In the following description, numerous specific details are set forth, such as specific configurations, dimensions and processes, etc., in order to provide a thorough understanding of the present invention. In other instances, well-known semiconductor processes and manufacturing techniques have not been described in particular detail in order to not unnecessarily obscure the present invention. Reference throughout this specification to “one embodiment” means that a particular feature, structure, configuration, or characteristic described in connection with the embodiment is included in at least one embodiment of the invention. Thus, the appearances of the phrase “in one embodiment” in various places throughout this specification are not necessarily referring to the same embodiment of the invention. Furthermore, the particular features, structures, configurations, or characteristics may be combined in any suitable manner in one or more embodiments.

**[0031]** The terms “spanning”, “over”, “to”, “between” and “on” as used herein may refer to a relative position of one layer with respect to other layers. One layer “spanning”, “over” or “on” another layer or bonded “to” or in “contact” with another layer may be directly in contact with the other layer or may have one or more intervening layers. One layer “between” layers may be directly in contact with the layers or may have one or more intervening layers.

**[0032]** Referring now to FIGS. 3A-3B an embodiment is illustrated in which a backplane similar to an AMOLED backplane is modified to receive emissive micro LED devices rather than an organic emission layer. FIG. 3A is a top view illustration of an active matrix display panel in accordance with an embodiment, and FIG. 3B is a side-view illustration of the active matrix display panel of FIG. 3A taken along lines X-X and Y-Y in accordance with an embodiment of the invention. In such an embodiment, the underlying TFT substrate **102** can be similar to those in a typical AMOLED backplane described with regard to FIGS. 1-2 including working circuitry (e.g. T1, T2) and planarization layer **122**. Openings **131** may be formed in the planarization layer **122** to contact the working circuitry. The working circuitry can include traditional 2T1C (two transistors, one capacitor) circuits including a switching transistor, a driving transistor, and a storage capacitor. It is to be appreciated that the 2T1C circuitry is meant to be exemplary, and that other types of circuitry or modifications of the traditional 2T1C circuitry are contemplated in accordance with embodiments of the invention. For example, more complicated circuits can be used to compensate for process variations of the driver transistor and the light emitting device, or for their instabilities. Furthermore, while embodiments of the invention are described and illustrated with regard to top gate transistor structures in the TFT substrate **102**, embodiments of the invention also contemplate the

use of bottom gate transistor structures. Likewise, while embodiments of the invention are described and illustrated with regard to a top emission structure, embodiments of the invention also contemplate the use of bottom, or both top and bottom emission structures. In addition, embodiments of the invention are described and illustrated below specifically with regard to a high side drive configuration including a ground ring. In a high side drive configuration a LED may be on the drain side of a PMOS driver transistor or a source side of an NMOS driver transistor so that the circuit is pushing current through the p-terminal of the LED. Embodiments of the invention are not so limited may also be practiced with a low side drive configuration in which case the ground ring become the power line in the panel and current is pulled through the n-terminal of the LED.

**[0033]** A patterned bank layer **126** including bank openings **148** is then formed over the planarization layer **122**. Bank layer **126** may be formed by a variety of techniques such as ink jet printing, screen printing, lamination, spin coating, CVD, and PVD. Bank layer **126** may be opaque, transparent, or semi-transparent to the visible wavelength. Bank layer **126** may be formed of a variety of insulating materials such as, but not limited to, photodefinable acrylic, photoresist, silicon oxide (SiO<sub>2</sub>), silicon nitride (SiN<sub>x</sub>), poly (methyl methacrylate) (PMMA), benzocyclobutene (BCB), polyimide, acrylate, epoxy, and polyester. In an embodiment, bank layer is formed of an opaque material such as a black matrix material. Exemplary insulating black matrix materials include organic resins, glass pastes, and resins or pastes including a black pigment, metallic particles such as nickel, aluminum, molybdenum, and alloys thereof, metal oxide particles (e.g. chromium oxide), or metal nitride particles (e.g. chromium nitride).

**[0034]** In accordance with embodiments of the invention, the thickness of the bank layer **126** and width of the bank openings **128** described with regard to the following figures may depend upon the height of the micro LED device to be mounted within the opening, height of the transfer heads transferring the micro LED devices, and resolution. In an embodiment, the resolution, pixel density, and subpixel density of the display panel may account for the width of the bank openings **128**. For an exemplary 55 inch television with a 40 PPI (pixels per inch) and 211  $\mu\text{m}$  subpixel pitch, the bank opening **128** width may be anywhere from a few microns to 206  $\mu\text{m}$  to account for an exemplary 5  $\mu\text{m}$  wide surrounding bank structure. For an exemplary display panel with 440 PPI and a 19  $\mu\text{m}$  subpixel pitch, the bank opening **128** width may be anywhere from a few microns to 15  $\mu\text{m}$  to account for an exemplary 5  $\mu\text{m}$  wide surrounding bank structure. Width of the bank structure (i.e. between bank openings **128**) may be any suitable size, so long as the structure supports the required processes and is scalable to the required PPI.

**[0035]** In accordance with embodiments of the invention, the thickness of the bank layer **126** is not too thick in order for the bank structure to function. Thickness may be determined by the micro LED device height and a predetermined viewing angle. For example, where sidewalls of the bank openings **128** make an angle with the planarization layer **122**, shallower angles may correlate to a wider viewing angle of the system. In an embodiment, exemplary thicknesses of the bank layer **126** may be between 1  $\mu\text{m}$ -50  $\mu\text{m}$ .

**[0036]** A patterned conductive layer is then formed over the patterned bank layer **126**. Referring to FIG. 3B, in one embodiment the patterned conductive layer includes bottom

electrodes **142** formed within the bank openings **148** and in electrical contact with the working circuitry. The patterned conductive layer may also optionally include the ground ring **116**. As used herein the term ground “ring” does not require a circular pattern, or a pattern that completely surrounds an object. Rather, the term ground “ring” means a pattern that at least partially surrounds the pixel area on three sides. In addition, while the following embodiments are described and illustrated with regard to a ground ring **116**, it is to be appreciated that embodiments of the invention can also be practiced with a ground line running along one side (e.g. left, right, bottom, top), or two sides (a combination of two of the left, right, bottom, top) of the pixel area. Accordingly, it is to be appreciated that in the following description the reference to and illustration of a ground ring could potentially be replaced with a ground line where system requirements permit.

**[0037]** The patterned conductive layer may be formed of a number of conductive and reflective materials, and may include more than one layer. In an embodiment, a patterned conductive layer comprises a metallic film such as aluminum, molybdenum, titanium, titanium-tungsten, silver, or gold, or alloys thereof. The patterned conductive layer may include a conductive material such as amorphous silicon, transparent conductive oxides (TCO) such as indium-tin-oxide (ITO) and indium-zinc-oxide (IZO), carbon nanotube film, or a transparent conducting polymer such as poly(3,4-ethylenedioxythiophene) (PEDOT), polyaniline, polyacetylene, polypyrrole, and polythiophene. In an embodiment, the patterned conductive layer includes a stack of a conductive material and a reflective conductive material. In an embodiment, the patterned conductive layer includes a 3-layer stack including top and bottom layers and a reflective middle layer wherein one or both of the top and bottom layers are transparent. In an embodiment, the patterned conductive layer includes a conductive oxide-reflective metal-conductive oxide 3-layer stack. The conductive oxide layers may be transparent. For example, the patterned conductive layer may include an ITO-silver-ITO layer stack. In such a configuration, the top and bottom ITO layers may prevent diffusion and/or oxidation of the reflective metal (silver) layer. In an embodiment, the patterned conductive layer includes a Ti—Al—Ti stack, or a Mo—Al—Mo-ITO stack. In an embodiment, the patterned conductive layer includes a ITO—Ti—Al—Ti-ITO stack. In an embodiment, the patterned conductive layer is 1  $\mu\text{m}$  or less in thickness. The patterned conductive layer may be deposited using a suitable technique such as, but not limited to, PVD.

**[0038]** Following the formation of bottom electrodes **142** and ground ring **116**, an insulator layer **146** may then optionally be formed over the TFT substrate **102** covering the sidewalls of the patterned conductive layer. The insulator layer **146** may at least partially cover the bank layer **126** and the reflective layer forming the bottom electrodes **142**, and optionally the ground ring **116**.

**[0039]** In an embodiment, the insulator layer **146** is formed by blanket deposition using a suitable technique such as lamination, spin coating, CVD, and PVD, and then patterned using a suitable technique such as lithography to form openings exposing the bottom electrodes **142**, and optionally openings **130** exposing the ground ring **116**. In an embodiment, ink jet printing or screen printing may be used to form the insulator layer **146** and optionally openings **130** without requiring lithography. Insulator layer **146** may be formed of a variety of materials such as, but not limited to,  $\text{SiO}_2$ ,  $\text{SiN}_x$ ,

PMMA, BCB, polyimide, acrylate, epoxy, and polyester. For example, the insulator layer **146** may be 0.5  $\mu\text{m}$  thick. The insulator layer **146** may be transparent or semi-transparent where formed over the reflective layer on sidewalls of bottom electrode **142** within the bank openings **128** as to not significantly degrade light emission extraction of the completed system. Thickness of the insulator layer **146** may also be controlled to increase light extraction efficiency, and also to not interfere with the array of transfer heads during transfer of the array of light emitting devices to the reflective bank structure. As will become more apparent in the following description, the patterned insulator layer **146** is optional, and represents one manner for electrically separating, or passivating the sidewalls of conductive layers.

**[0040]** In the embodiment illustrated in FIG. 3B, the bottom electrodes **142** and ground ring **116** can be formed of the same conductive layer. In another embodiment, the ground ring **116** can be formed of a conductive material different from the bottom electrodes **142**. For example, ground ring **116** may be formed with a material having a higher conductivity than the bottom electrodes **142**. In another embodiment, ground ring **116** can also be formed within different layers from the bottom electrodes. FIGS. 3C-3D illustrate embodiments where the ground ring **116** can be formed within or below the patterned bank layer **126**. For example, in the embodiment illustrated in FIG. 3C, openings **130** may be formed through the patterned bank layer **126** when forming the ground ring **116**. In the embodiment illustrated in FIG. 3D, openings **130** may be formed through the patterned bank layer **126** and planarization layer **122** to contact the ground ring **116** which may have been formed during formation of the working circuitry of the TFT substrate **102**. In such an embodiment the conductive layer used to form the bottom electrode **142** may also optionally also be formed within the opening **130** to further enable electrical contact of the top electrode layer yet to be formed with the ground ring **116** through openings **130**. Accordingly, it is to be appreciated that the embodiments illustrated in FIGS. 3A-3D are not limiting and that a number of possibilities exist for forming the ground ring **116**, as well as openings **130** to expose the ground ring **116**.

**[0041]** Still referring to embodiments illustrated in FIG. 3B-3D, a bonding layer **140** may be formed on the bottom electrode layer **142** to facilitate bonding of a micro LED device. In an embodiment, the bonding layer **140** is selected for its ability to be inter-diffused with a bonding layer on the micro LED device (yet to be placed) through bonding mechanisms such as eutectic alloy bonding, transient liquid phase bonding, or solid state diffusion bonding as described in U.S. patent application Ser. No. 13/749,647. In an embodiment, the bonding layer **140** has a melting temperature of 250° C. or lower. For example, the bonding layer **140** may include a solder material such as tin (232° C.) or indium (156.7° C.), or alloys thereof. Bonding layer **140** may also be in the shape of a post, having a height greater than width. In accordance with some embodiments of the invention, taller bonding layers **140** may provide an additional degree of freedom for system component leveling, such as planarity of the array of micro LED devices with the TFT substrate during the micro LED device transfer operation and for variations in height of the micro LED devices, due to the change in height of the liquefied bonding layers as they spread out over the surface during bonding, such as during eutectic alloy bonding and transient liquid phase bonding. The width of the bonding layers **140**

may be less than a width of a bottom surface of the micro LEDs to prevent wicking of the bonding layers 140 around the sidewalls of the micro LEDs and shorting the quantum well structures.

[0042] FIGS. 4A-4H are cross-sectional side view illustrations for a method of transferring an array of micro LED devices to the TFT substrate 102 in accordance with an embodiment of the invention. Referring to FIG. 4A, an array of transfer heads 302 supported by a transfer head substrate 300 are positioned over an array of micro LED devices 400 supported on a carrier substrate 200. A heater 306 and heat distribution plate 304 may optionally be attached to the transfer head substrate 300. A heater 204 and heat distribution plate 202 may optionally be attached to the carrier substrate 200. The array of micro LED devices 400 are contacted with the array of transfer heads 302, as illustrated in FIG. 4B, and picked up from the carrier substrate 200 as illustrated in FIG. 4C. In an embodiment, the array of micro LED devices 400 are picked up with an array of transfer heads 302 operating in accordance with electrostatic principles, that is, they are electrostatic transfer heads.

[0043] FIG. 4D is a cross-sectional side view illustration of a transfer head 302 holding a micro LED device 400 over a TFT substrate 102 in accordance with an embodiment of the invention. In the embodiment illustrated, the transfer head 302 is supported by a transfer head substrate 300. As described above, a heater 306 and heat distribution plate 304 may optionally be attached to the transfer head substrate to apply heat to the transfer head 302. A heater 152 and heat distribution plate 150 may also, or alternatively, optionally be used to transfer heat to the bonding layer 140 on the TFT substrate 102 and/or optional bonding layer 410 on a micro LED device 400 described below.

[0044] Still referring to FIG. 4D, a close-up view of an exemplary micro LED device 400 is illustrated in accordance with an embodiment. It is to be appreciated, that the specific micro LED device 400 illustrated is exemplary and that embodiments of the invention are not limited. In the particular embodiment illustrated, the micro LED device 400 includes a micro p-n diode 450 and a bottom conductive contact 420. A bonding layer 410 may optionally be formed below the bottom conductive contact 420, with the bottom conductive contact 420 between the micro p-n diode 450 and the bonding layer 410. In an embodiment, the micro LED device 400 further includes a top conductive contact 452. In an embodiment, the micro p-n diode 450 includes a top n-doped layer 414, one or more quantum well layers 416, and a lower p-doped layer 418. In other embodiments, the arrangement of n-doped and p-doped layers can be reversed. The micro p-n diodes can be fabricated with straight sidewalls or tapered sidewalls. In certain embodiments, the micro p-n diodes 450 possess outwardly tapered sidewalls 453 (from top to bottom). In certain embodiments, the micro p-n diodes 450 possess inwardly tapered sidewall (from top to bottom). The top and bottom conductive contacts 420, 452. For example, the bottom conductive contact 420 may include an electrode layer and a barrier layer between the electrode layer and the optional bonding layer 410. The top and bottom conductive contacts 420, 452 may be transparent to the visible wavelength range (e.g. 380 nm-750 nm) or opaque. The top and bottom conductive contacts 420, 452 may optionally include a reflective layer, such as a silver layer. The micro p-n diode and conductive contacts may each have a top surface, a bottom surface and sidewalls. In an embodiment, the bottom

surface 451 of the micro p-n diode 450 is wider than the top surface of the micro p-n diode, and the sidewalls 453 are tapered outwardly from top to bottom. The top surface of the micro p-n diode 450 may be wider than the bottom surface of the p-n diode, or approximately the same width. In an embodiment, the bottom surface 451 of the micro p-n diode 450 is wider than the top surface of the bottom conductive contact 420. The bottom surface of the micro p-n diode may also be approximately the same width as the top surface of the bottom conductive contact 420. In an embodiment, the micro p-n diode 450 is several microns thick, such as 3  $\mu\text{m}$  or 5  $\mu\text{m}$ , the conductive contacts 420, 452 are 0.1  $\mu\text{m}$ -2  $\mu\text{m}$  thick, and the optional bonding layer 410 is 0.1  $\mu\text{m}$ -1  $\mu\text{m}$  thick. In an embodiment, a maximum width of each micro LED device 400 is 1-100  $\mu\text{m}$ , for example, 30  $\mu\text{m}$ , 10  $\mu\text{m}$ , or 5  $\mu\text{m}$ . In an embodiment, the maximum width of each micro LED device 400 must comply with the available space in the bank opening 128 for a particular resolution and PPI of the display panel.

[0045] FIG. 4E is a cross-sectional side view illustration of an array of transfer heads holding an array micro LED devices 400 over a TFT substrate 102 accordance with an embodiment of the invention. FIG. 4E is substantially similar to the structure illustrated in FIG. 4D with the primary difference being the illustration of the transfer of an array of micro LED devices as opposed to a single micro LED device within the array of micro LED devices.

[0046] Referring now to FIG. 4F the TFT substrate 102 is contacted with the array of micro LED devices 400. In the embodiment illustrated, contacting the TFT substrate 102 with the array of micro LED devices 400 includes contacting bonding layer 140 with a micro LED device bonding layer 410 for each respective micro LED device. In an embodiment, each micro LED device bonding layer 410 is wider than a corresponding bonding layer 140. In an embodiment energy is transferred from the electrostatic transfer head assembly and through the array of micro LED devices 400 to bond the array of micro LED devices 400 to the TFT substrate 102. For example, thermal energy may be transferred to facilitate several types of bonding mechanisms such as eutectic alloy bonding, transient liquid phase bonding, and solid state diffusion bonding. The transfer of thermal energy may also be accompanied by the application of pressure from the electrostatic transfer head assembly.

[0047] Referring to FIG. 4G, in an embodiment, the transfer of energy liquefies bonding layer 140. The liquefied bonding layer 140 may act as a cushion and partially compensate for system uneven leveling (e.g. nonplanar surfaces) between the array of micro devices 400 and the TFT substrate during bonding, and for variations in height of the micro LED devices. In the particular implementation of transient liquid phase bonding the liquefied bonding layer 140 inter-diffuses with the micro LED device bonding layer 410 to form an inter-metallic compound layer with an ambient melting temperature higher than the ambient melting temperature of the bonding layer 140. Accordingly, transient liquid phase bonding may be accomplished at or above the lowest liquidus temperature of the bonding layers. In some embodiments of the invention, the micro LED device bonding layer 410 is formed of a material having a melting temperature above 250° C. such as bismuth (271.4° C.), or a melting temperature above 350° C. such as gold (1064° C.), copper (1084° C.), silver (962° C.), aluminum (660° C.), zinc (419.5° C.), or

nickel (1453° C.), and the TFT substrate bonding layer **140** has a melting temperature below 250° C. such as tin (232° C.) or indium (156.7° C.).

**[0048]** In this manner, the substrate **150** supporting the TFT substrate **102** can be heated to a temperature below the melting temperature of the bonding layer **140**, and the substrate **304** supporting the array of transfer heads is heated to a temperature below the melting temperature of bonding layer **410**, but above the melting temperature of bonding layer **140**. In such an embodiment, the transfer of heat from the electrostatic transfer head assembly through the array of micro LED devices **400** is sufficient to form the transient liquid state of bonding layer **140** with subsequent isothermal solidification as an inter-metallic compound. While in the liquid phase, the lower melting temperature material both spreads out over the surface and diffused into a solid solution of the higher melting temperature material or dissolves the higher melting temperature material and solidifies as an inter-metallic compound. In a specific embodiment, the substrate **304** supporting the array of transfer heads is held at 180° C., bonding layer **410** is formed of gold, and bonding layer **140** is formed of indium.

diode **450** may include a material such as indium gallium nitride (InGaN), gallium nitride (GaN), gallium phosphide (GaP), aluminum gallium indium phosphide (AlGaInP), and aluminum gallium phosphide (AlGaP). Referring to FIG. **5C**, a third transfer procedure has been completed for transferring an array of blue-emitting micro LED devices **400B** from a third carrier substrate to the TFT substrate **102**. For example, where the micro LED devices **400B** are designed to emit a blue light (e.g. 450-495 nm wavelength) the micro p-n diode **450** may include a material such as gallium nitride (GaN), indium gallium nitride (InGaN), and zinc selenide (ZnSe).

**[0051]** In accordance with embodiments of the invention, the transfer heads are separated by a pitch (x, y, and/or diagonal) that matches a pitch of the bank openings on the backplane corresponding to the pixel or subpixel array. Table 1 provides a list of exemplary implementations in accordance with embodiments of the invention for various red-green-blue (RGB) displays with 1920×1080p and 2560×1600 resolutions. It is to be appreciated that embodiments of the invention are not limited to RGB color schemes or the 1920×1080p or 2560×1600 resolutions, and that the specific resolution and RGB color scheme is for illustrational purposes only.

TABLE 1

Display Substrate	Pixel Pitch (x, y)	Sub-Pixel pitch (x, y)	Pixels per inch (PPI)	Possible transfer head array pitch
55"	(634 μm,	(211 μm,	40	X: Multiples or fractions of 211 μm
1920 × 1080	634 μm)	634 μm)		Y: Multiples or fractions of 634 μm
10"	(85 μm,	(28 μm,	299	X: Multiples or fractions of 28 μm
2560 × 1600	85 μm)	85 μm)		Y: Multiples or fractions of 85 μm
4"	(78 μm,	(26 μm,	326	X: Multiples or fractions of 26 μm
640 × 1136	78 μm)	78 μm)		Y: Multiples or fractions of 78 μm
5"	(58 μm,	(19 μm,	440	X: Multiples or fractions of 19 μm
1920 × 1080	58 μm)	58 μm)		Y: Multiples or fractions of 58 μm

**[0049]** Following the transfer of energy to bond the array of micro LED devices **400** to the TFT substrate, the array of micro LED devices **400** are released onto the receiving substrate and the array of electrostatic transfer heads are moved away as illustrated in FIG. **4H**. Releasing the array of micro LED devices **400** may be accomplished with a variety of methods including turning off the electrostatic voltage sources, lowering the voltage across the electrostatic transfer head electrodes, changing a waveform of an AC voltage, and grounding the voltage sources.

**[0050]** Referring now to FIGS. **5A-5C**, a sequence of transferring an array of micro LED devices **400** with different color emissions is illustrated in accordance with an embodiment of the invention. In the particular configuration illustrated in FIG. **5A**, a first transfer procedure has been completed for transferring an array of red-emitting micro LED devices **400R** from a first carrier substrate to the TFT substrate **102**. For example, where the micro LED devices **400R** are designed to emit a red light (e.g. 620-750 nm wavelength) the micro p-n diode **450** may include a material such as aluminum gallium arsenide (AlGaAs), gallium arsenide phosphide (GaAsP), aluminum gallium indium phosphide (AlGaInP), and gallium phosphide (GaP). Referring to FIG. **5B**, a second transfer procedure has been completed for transferring an array of green-emitting micro LED devices **400G** from a second carrier substrate to the TFT substrate **102**. For example, where the micro LED devices **400G** are designed to emit a green light (e.g. 495-570 nm wavelength) the micro p-n

**[0052]** In the above exemplary embodiments, the 40 PPI pixel density may correspond to a 55 inch 1920×1080p resolution television, and the 326 and 440 PPI pixel density may correspond to a handheld device with RETINA® display. In accordance with embodiments of the invention, thousands, millions, or even hundreds of millions of transfer heads can be included in a micro pick up array of a mass transfer tool depending upon the size of the micro pick up array. In accordance with embodiments of the invention, a 1 cm×1.12 cm array of transfer heads can include 837 transfer heads with a 211 μm, 634 μm pitch, and 102,000 transfer heads with a 19 μm, 58 μm pitch.

**[0053]** The number of micro LED devices picked up with the array of transfer heads may or may not match the pitch of transfer heads. For example, an array of transfer heads separated by a pitch of 19 μm picks up an array of micro LED devices with a pitch of 19 μm. In another example, an array of transfer heads separated by a pitch of 19 μm picks up an array of micro LED devices with a pitch of approximately 6.33 μm. In this manner the transfer heads pick up every third micro LED device for transfer to the backplane. In accordance with some embodiments, the top surface of the array of light emitting micro devices is higher than the top surface of the insulator layer **146** so as to prevent the transfer heads from being damaged by or damaging the insulator layer (or any intervening layer) on the backplane during placement of the micro LED devices within bank openings.



[0054] FIG. 6A is a top view illustration of an active matrix display panel in accordance with an embodiment after the formation of a top electrode layer. FIG. 6B is a top view illustration of an active matrix display panel in accordance with an embodiment after the formation of separate top electrode layers. FIGS. 6C-6D are side-view illustrations of the active matrix display panel of either FIG. 6A or FIG. 6B taken along lines X-X and Y-Y in accordance with embodiments of the invention. In accordance with the embodiments illustrated in FIGS. 6A-6B, one or more top electrode layers 118 are formed over the pixel area 104 including the array of micro LED devices 400 as well as in the non-pixel area and overlapping the ground ring 116.

[0055] Referring now to FIGS. 6C-6D, prior to forming the one or more top electrode layers 118 the micro LED devices 400 are passivated within the bank openings 128 in order to prevent electrical shorting between the top and bottom electrode layers 118, 142, or shorting at the one or more quantum wells 416. As illustrated, after the transfer of the array micro LED devices 400, a passivation layer 148 may be formed around the sidewalls of the micro LED devices 400 within the array of bank openings 128. In an embodiment, where the micro LED devices 400 are vertical LED devices, the passivation layer 148 covers and spans the quantum well structure 416. The passivation layer 148 may also cover any portions of the bottom electrode layer 142 not already covered by the optional insulator layer 146 in order to prevent possible shorting. Accordingly, the passivation layer 148 may be used to passivate the quantum well structure 416, as well as the bottom electrode layer. In accordance with embodiments of the invention, the passivation layer 148 is not formed on the top surface of the micro LED devices 400, such as top conductive contact 452. In one embodiment, a plasma etching process, e.g. O<sub>2</sub> or CF<sub>4</sub> plasma etch, can be used after forming the passivation layer 148 to etch back the passivation layer 148, ensuring the top surface of the micro LED devices 400, such as top conductive contacts 452, are exposed to enable the top conductive electrode 118 layers 118 to make electrical contact with the micro LED devices 400.

[0056] In accordance with embodiments of the invention, the passivation layer 148 may be transparent or semi-transparent to the visible wavelength so as to not significantly degrade light extraction efficiency of the completed system. Passivation layer may be formed of a variety of materials such as, but not limited to epoxy, acrylic (polyacrylate) such as poly(methyl methacrylate) (PMMA), benzocyclobutene (BCB), polyimide, and polyester. In an embodiment, passivation layer 148 is formed by ink jet printing or screen printing around the micro LED devices 400.

[0057] In the particular embodiment illustrated in FIG. 6C, the passivation layer 148 is only formed within the bank openings 128. However, this is not required, and the passivation layer 148 may be formed on top of the bank structure layer 126. Furthermore, the formation of insulator layer 146 is not required, and passivation layer 148 can also be used to electrically insulate the conductive layers. As shown in the embodiment illustrated in FIG. 6D, the passivation layer 148 may also be used to passivate sidewalls of the conductive layer forming the bottom electrode 142. In an embodiment, passivation layer 148 may optionally be used to passivate ground ring 116. In accordance with some embodiments, the formation of openings 130 can be formed during the process of ink jet printing or screen printing the passivation layer 148

over the ground ring 116. In this manner, a separate patterning operation may not be required to form the openings 130.

[0058] In accordance with some embodiments of the invention a canal 151, or well structure, can be formed within the bank layer 126 as illustrated in FIG. 6D in order to capture or prevent the passivation layer 148 from spreading excessively and overflowing over the ground tie lines 149, particularly when the passivation layer 148 is formed using a solvent system such as with ink jet printing or screen printing. Accordingly, in some embodiments, a canal 151 is formed within the bank layer 126 between the bank opening 128 and an adjacent ground tie line 144.

[0059] Still referring to FIGS. 6C-6D, after formation of passivation layer 148 one or more top conductive electrode layers 118 are formed over each micro LED device 400 and in electrical contact with the top contact layer 452, if present. Depending upon the particular application in the following description, top electrode layers 118 may be opaque, reflective, transparent, or semi-transparent to the visible wavelength. For example, in top emission systems the top electrode layer 118 may be transparent, and for bottom emission systems the top electrode layer may be reflective. Exemplary transparent conductive materials include amorphous silicon, transparent conductive oxides (TCO) such as indium-tin-oxide (ITO) and indium-zinc-oxide (IZO), carbon nanotube film, or a transparent conductive polymer such as poly(3,4-ethylenedioxythiophene) (PEDOT), polyaniline, polyacetylene, polypyrrole, and polythiophene. In an embodiment, the top electrode layer 118 includes nanoparticles such as silver, gold, aluminum, molybdenum, titanium, tungsten, ITO, and IZO. In a particular embodiment, the top electrode layer 118 is formed by ink jet printing or screen printing ITO or a transparent conductive polymer such as PEDOT. Other methods of formation may include chemical vapor deposition (CVD), physical vapor deposition (PVD), spin coating. The top electrode layer 118 may also be reflective to the visible wavelength. In an embodiment, a top conductive electrode layer 118 comprises a reflective metallic film such as aluminum, molybdenum, titanium, titanium-tungsten, silver, or gold, or alloys thereof, for example for use in a bottom emission system.

[0060] Referring back to FIG. 6A again, in the particular embodiment illustrated a top electrode layer 118 is formed over the pixel area 104 including the array of micro LED devices 400 as well as in the non-pixel area and overlapping the ground ring 116. The top electrode layer 118 may also be formed within the openings 130, if present, and over the ground ring 116.

[0061] FIG. 6B illustrates an alternative embodiment in which separate top electrode layers 118 are formed connecting one or more rows of micro LED devices 400 with the ground ring. In the particular embodiment illustrated, the top electrode layers 118 provide the electrical path from a micro LED device 400 to the ground ring. It is not required for the top electrode layers 118 to cover the entire pixel area 104, or the entire bank opening 128. In the particular embodiment illustrated, each top electrode layer 118 is connected to opposite sides of the ground ring 116 and runs horizontally across the TFT substrate connecting a single row of micro LEDs 400. However, this particular configuration is exemplary and a number of different arrangements are possible. For example, a single top electrode layer 118 may run over, and electrically connect an n-number of rows of micro LEDs to the ground ring. In another embodiment, the top electrode

layers **118** are only connected to one side of the ground ring **116**, or ground line. As illustrated in FIGS. **6A-6B**, ink jet line width for the top electrode layers **118** can vary depending upon application. For example, the line width may approach that of the pixel area **104**. Alternatively, the line width may be minimal. For example, line widths as low as approximately 15  $\mu\text{m}$  may be accomplished with commercially available ink jet printers. Accordingly, the line width of the top electrode layers **118** may be more or less than the maximum width of the micro LED devices.

**[0062]** In one aspect, the particular embodiment illustrated in FIG. **6B** may be particularly suitable for localized formation of the top electrode layers **118** with ink jet printing or screen printing. Conventional AMOLED backplane processing sequences such as those used for the fabrication of the display panels in FIGS. **1-2** typically blanket deposit the top electrode layer in deposition a chamber, followed by singulation of the individual backplanes from a larger substrate. In accordance with some embodiments, the display panel/backplane **100** is singulated from a larger substrate prior to transferring the array of micro LED devices **400**. In an embodiment, ink jet printing or screen printing provides a practical approach for patterning the individual top electrode layers **118** without requiring a separate mask layer for each separate display panel backplane **100**.

**[0063]** While not illustrated separately it is to be appreciated that the embodiments illustrated in FIGS. **6A-6D** are combinable with the alternative opening configurations included in FIGS. **3C-3D**.

**[0064]** FIG. **7** illustrates a display system **700** in accordance with an embodiment. The display system houses a processor **710**, data receiver **720**, a display panel **100**, such as any of the display panels described above. The data receiver **720** may be configured to receive data wirelessly or wired. Wireless may be implemented in any of a number of wireless standards or protocols including, but not limited to, Wi-Fi (IEEE 802.11 family), WiMAX (IEEE 802.16 family), IEEE 802.20, long term evolution (LTE), Ev-DO, HSPA+, HSDPA+, HSUPA+, EDGE, GSM, GPRS, CDMA, TDMA, DECT, Bluetooth, derivatives thereof, as well as any other wireless protocols that are designated as 3G, 4G, 5G, and beyond.

**[0065]** Depending on its applications, the display system **700** may include other components. These other components include, but are not limited to, memory, a touch-screen controller, and a battery. In various implementations, the display system **700** may be a television, tablet, phone, laptop, computer monitor, kiosk, digital camera, handheld game console, media display, ebook display, or large area signage display.

**[0066]** In utilizing the various aspects of this invention, it would become apparent to one skilled in the art that combinations or variations of the above embodiments are possible for integrating micro LED devices into an active matrix display panel. While the above embodiments have been described with regard to a top emission structure, embodiments of the invention are also applicable to bottom emission structures. For example, rather than locating the bank openings **128** or subpixel openings **127** above the TFT circuitry, the openings could be located adjacent the TFT circuitry on lower layers in the TFT substrate **102**. Similarly, while top gate transistor structures have been described, embodiments of the invention may also be practiced with bottom gate transistor structures. Furthermore, while embodiments of the invention have been described and illustrated with regard to a high side drive configuration, embodiments may also be prac-

ticed with a low side drive configuration in which the ground ring described above becomes the power line in the panel. Although the present invention has been described in language specific to structural features and/or methodological acts, it is to be understood that the invention defined in the appended claims is not necessarily limited to the specific features or acts described. The specific features and acts disclosed are instead to be understood as particularly graceful implementations of the claimed invention useful for illustrating the present invention.

What is claimed is:

1. An active matrix display panel comprising:
  - a thin film transistor (TFT) substrate including a pixel area and a non-pixel area, wherein the pixel area includes an array of bank openings and an array of bottom electrodes within the array of bank openings;
  - a ground line in the non-pixel area;
  - an array of micro LED devices on the array of bottom electrodes within the corresponding array of bank openings; and
  - an array of top electrode layers electrically connecting the array of micro LED devices to the ground line.
2. The display panel of claim 1, wherein the ground line is a ground ring in the non-pixel area around the pixel area.
3. The display panel of claim 2, wherein the array of top electrode layers are electrically connected to the ground ring on opposite sides of the pixel area.
4. The display panel of claim 3, wherein each top electrode layer spans over a single row of micro LED devices.
5. The display panel of claim 3, wherein each top electrode layer spans over a plurality of rows of micro LED devices.
6. The display panel of claim 1, wherein the pixel area is not completely covered by the array of top electrode layers.
7. The display panel of claim 1, wherein the array of bottom electrodes are formed on sidewalls of the corresponding array of bank openings.
8. The display panel of claim 7, wherein the bottom electrodes are reflective to the visible wavelength range.
9. The display panel of claim 1, further comprising a patterned insulator layer covering the array of bottom electrodes, and an array of openings in the patterned insulator layer exposing the array of bottom electrodes.
10. The display panel of claim 9, wherein the patterned insulator layer covers edges of the array of bottom electrodes.
11. The display panel of claim 1, wherein the micro LED devices are vertical micro LED devices.
12. The display panel of claim 11, wherein the micro LED devices each have a maximum width of 1  $\mu\text{m}$ -100  $\mu\text{m}$ .
13. The display panel of claim 12, further comprising a transparent passivation layer spanning sidewalls of the array of micro LED devices within the array of bank openings, wherein the transparent passivation layer does not completely cover a top conductive contact of each micro LED device.
14. The display panel of claim 1, wherein the array of top electrode layers are formed of a transparent or semi-transparent material.
15. The display panel of claim 14, wherein the array of top electrode layers comprise a material selected from the group consisting of PEDOT and ITO.
16. A method of forming a display panel comprising:
  - transferring an array of micro LED devices from a carrier substrate to a backplane that comprises:
    - a thin film transistor (TFT) substrate including a pixel area and a non-pixel area, wherein the pixel area

includes an array of bank openings and an array of bottom electrodes within the array of bank openings; and

a ground line in the non-pixel area; and

bonding the array of micro LED devices to the array of bottom electrodes; and

forming an array of top electrode layers electrically connecting the array of micro LED devices to the ground line.

**17.** The method of claim **16**, wherein forming the array of top electrode layers comprises ink jet printing or screen printing.

**18.** The method of claim **17**, wherein the ground line is a ground ring, and further comprising ink jet printing or screen printing the array of top electrode layers spanning between opposite sides of the ground ring.

**19.** The method of claim **16**, further comprising ink jet printing or screen printing each top electrode layer spanning over a single row of micro LED devices.

**20.** The method of claim **16**, further comprising ink jet printing or screen printing each top electrode layer spanning over a plurality of rows of micro LED devices.

**21.** The method of claim **16**, wherein transferring the array of micro LED devices comprises transferring the array of micro LED devices with an array of electrostatic transfer heads.

**22.** The method of claim **21**, wherein bonding the array of micro LED devices to the array of bottom electrodes comprises the formation of an inter-metallic compound.

**23.** The method of claim **21**, wherein bonding the array of micro LED devices to the array of bottom electrodes comprises liquefying an array of bonding layers formed on the array of bottom electrodes.

**24.** The method of claim **21**, wherein bonding the array of micro LED devices comprises transferring thermal energy from an array of electrostatic transfer heads to the array of bonding layers formed on the array of bottom electrodes.

**25.** The method of claim **16**, further comprising ink jet printing or screen printing a passivation layer within each bank opening to cover a quantum well structure in each micro LED device.

**26.** The method of claim **25**, further comprising ink jet printing or screen printing the passivation layer within each bank opening to cover all exposed portions of the bottom electrode for each bank opening.

\* \* \* \* \*

专利名称(译)	有源矩阵发光微LED显示屏		
公开(公告)号	<a href="#">US20140159067A1</a>	公开(公告)日	2014-06-12
申请号	US13/842721	申请日	2013-03-15
[标]申请(专利权)人(译)	勒克斯维科技公司		
申请(专利权)人(译)	LUXVUE科技股份有限公司		
当前申请(专利权)人(译)	LUXVUE科技股份有限公司		
[标]发明人	SAKARIYA KAPIL V BIBL ANDREAS HU HSIN HUA		
发明人	SAKARIYA, KAPIL V. BIBL, ANDREAS HU, HSIN-HUA		
IPC分类号	H01L27/12		
CPC分类号	H01L24/24 H01L24/29 H01L24/75 H01L24/82 H01L24/83 H01L24/95 H01L27/1214 H01L2224/29109 H01L2224/29111 H01L2224/29113 H01L2224/29118 H01L2224/29124 H01L2224/29139 H01L2224/29144 H01L2224/29147 H01L2224/29155 H01L2224/73267 H01L2224/75281 H01L2224/75282 H01L2224/75725 H01L2224/7598 H01L2224/83193 H01L2224/8381 H01L2224/83825 H01L2224/92244 H01L2924/01322 H01L2924/10156 H01L2924/12041 H01L2924/12044 H01L2924/00 H01L25/167 H01L33/06 H01L33/38 H01L33/42 H01L33/54 H01L33/62		
其他公开文献	US9159700		
外部链接	<a href="#">Espacenet</a> <a href="#">USPTO</a>		

# 摘要(译)

描述了显示面板和形成显示面板的方法。显示面板可以包括薄膜晶体管基板，该薄膜晶体管基板包括像素区域和非像素区域。像素区域包括堤开口阵列和堤开口阵列内的底电极阵列。微型LED器件阵列被结合到堤开口阵列内的相应的底部电极阵列。形成顶部电极层阵列，将微型LED器件阵列电连接到非像素区域中的地线。

